



R1Q3A7236ABB R1Q3A7218ABB

72-Mbit QDR™ II SRAM
4-word Burst

R10DS0165EJ0011

Rev. 0.11
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Description

The R1Q3A7236 is a 2,097,152-word by 36-bit and the R1Q3A7218 is a 4,194,304-word by 18-bit synchronous quad data rate static RAM fabricated with advanced CMOS technology using full CMOS six-transistor memory cell. It integrates unique synchronous peripheral circuitry and a burst counter. All input registers are controlled by an input clock pair (K and /K) and are latched on the positive edge of K and /K. These products are suitable for applications which require synchronous operation, high speed, low voltage, high density and wide bit configuration. These products are packaged in 165-pin plastic FBGA package.

Features

- Power Supply
 - 1.8 V for core (V_{DD}), 1.4 V to V_{DD} for I/O (V_{DDQ})
- Clock
 - Fast clock cycle time for high bandwidth
 - Two input clocks (K and /K) for precise DDR timing at clock rising edges only
 - Two input clocks for output data (C and /C) to minimize clock skew and flight time mismatches
 - Two output echo clocks (CQ and /CQ) simplify data capture in high-speed systems
 - Clock-stop capability with μ s restart
- I/O
 - Separate independent read and write data ports with concurrent transactions
 - 100% bus utilization DDR read and write operation
 - HSTL I/O
 - User programmable output impedance
 - DLL/PLL circuitry for wide output data valid window and future frequency scaling
- Function
 - Four-tick burst for reduced address frequency
 - Internally self-timed write control
 - Simple control logic for easy depth expansion
 - JTAG 1149.1 compatible test access port
- Package
 - 165 FBGA package (13 x 15 x 1.4 mm)

- Notes:
1. QDR RAMs and Quad Data Rate RAMs comprise a new family of products developed by Cypress Semiconductor, IDT, Samsung, and Renesas Electronics Corp. (QDR Co-Development Team)
 2. The specifications of this device are subject to change without notice. Please contact your nearest Renesas Electronics Sales Office regarding specifications.
 3. Refer to ["http://www.renesas.com/products/memory/fast_sram/qdr_sram/index.jsp"](http://www.renesas.com/products/memory/fast_sram/qdr_sram/index.jsp) for the latest and detailed information.
 4. Descriptions about x9 parts in this datasheet are just for reference.

Part Number Definition

| Column No. | 0 | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 | - | 12 | 13 | 14 | 15 | 16 |
|--|---|---|---|---|---|---|---|---|---|---|----|----|---|----|----|----|----|----|
| Example | R | 1 | Q | 3 | A | 7 | 2 | 1 | 8 | A | B | B | - | 3 | 0 | R | B | 0 |
| The above part number is just example for 72M QDR II B4 x18 333MHz, 13x15mm PKG, Pb-free part. | | | | | | | | | | | | | | | | | | |

| No. | - | Comments | No. | - | Comments | No. | - | Comments |
|-----|----------------------|---|-------|----------------|------------------------------|-----------------------|----|--|
| 0-1 | R1 | Renesas Memory Prefix | 4 | A | Vdd = 1.8 V | 12-13 | 60 | Frequency = 167MHz |
| 2-3 | Q2 | QDR II B2 ^[*1] (L15) ^[*2] | 5-6 | 36 | Density = 36Mb | | 50 | Frequency = 200MHz |
| | Q3 | QDR II B4 (L15) | | 72 | Density = 72Mb | | 40 | Frequency = 250MHz |
| | Q4 | DDR II B2 (L15) | 7-8 | 44 | Density = 144Mb | | 36 | Frequency = 275MHz |
| | Q5 | DDR II B4 (L15) | | 88 | Density = 288Mb | | 33 | Frequency = 300MHz |
| | Q6 | DDR II B2 SIO ^[*3] (L15) | 9 | 09 | Data width = 9bit | | 30 | Frequency = 333MHz |
| | QA | QDR II+ B4 L25 ^[*2] | | 18 | Data width = 18bit | | 27 | Frequency = 375MHz |
| | QB | DDR II+ B2 L25 | 10-11 | 36 | Data width = 36bit | | 25 | Frequency = 400MHz |
| | QC | DDR II+ B4 L25 | | R | 1st Generation | | 22 | Frequency = 450MHz |
| | QD | QDR II+ B4 L25 w/ODT ^[*4] | - | A | 2nd Generation | | 20 | Frequency = 500MHz |
| | QE | DDR II+ B2 L25 w/ODT | | B | 3rd Generation | | 19 | Frequency = 533MHz |
| | QF | DDR II+ B4 L25 w/ODT | | C | 4th Generation | | 18 | Frequency = 550MHz |
| | QG | QDR II+ B4 L20 | | D | 5th Generation | | 14 | R |
| | QH | DDR II+ B2 L20 | E | 6th Generation | I | | | Industrial temp. Ta range = -40°C to 85°C |
| | QJ | DDR II+ B4 L20 | F | 7th Generation | A | | | Pb and Tray |
| | QK | QDR II+ B4 L20 w/ODT | - | BG | PKG= BGA 15x17 mm | | 15 | B |
| | QL | DDR II+ B2 L20 w/ODT | | BB | PKG= BGA 13x15 mm | T | | Pb and Tape&Reel |
| QM | DDR II+ B4 L20 w/ODT | - | | - | S | Pb-free and Tape&Reel | | |
| QN | QDR II+ B2 L20 | - | | - | 0 to 9, A to Z or None | Renesas internal use | | |
| QP | QDR II+ B2 L20 w/ODT | - | - | - | - | - | | |
| - | - | - | - | - | - | - | - | - |

Note1: [*1] B=Burst length (B2: Burst length=2, B4: Burst length=4)
 [*2] L=Read Latency (L15: Read Latency = 1.5 cycle, L20: 2.0 cycle, L25: 2.5 cycle)
 [*3] SIO=Separate I/O
 [*4] ODT=On die termination

Note2: Package Marking Name
 Pb parts: Marking Name = Part Number(0-14)
 Pb-free parts: Marking Name = Part Number(0-14) + "PB-F"
 (Example) R1QAA4436RBG-20R ---- Pb parts
 R1QAA4436RBG-20R PB-F ---- Pb-free parts

Note3: Pb : RoHS Compliance Level = 5/6
 Pb-free: RoHS Compliance Level = 6/6

Note4: R1Q*A series support both "Commercial" and "Industrial" temperatures by "Industrial" temperature parts.

Pin Arrangement

R1Q3A7236 (Top) / R1QA(G)A7236 (Mid) / R1QD(K)A7236 (Bottom)

| | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 |
|---|-------|------------------|------------------|------------------|-----------------|-------------------|-----------------|------------------|------------------|------------------|-----|
| A | /CQ | NC | SA | /W | /BW2 | /K | /BW1 | /R | SA | NC | CQ |
| B | Q27 | Q18 | D18 | SA | /BW3 | K | /BW0 | SA | D17 | Q17 | Q8 |
| C | D27 | Q28 | D19 | V _{SS} | SA | NC | SA | V _{SS} | D16 | Q7 | D8 |
| D | D28 | D20 | Q19 | V _{SS} | V _{SS} | V _{SS} | V _{SS} | V _{SS} | Q16 | D15 | D7 |
| E | Q29 | D29 | Q20 | V _{DDQ} | V _{SS} | V _{SS} | V _{SS} | V _{DDQ} | Q15 | D6 | Q6 |
| F | Q30 | Q21 | D21 | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | D14 | Q14 | Q5 |
| G | D30 | D22 | Q22 | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | Q13 | D13 | D5 |
| H | /DOFF | V _{REF} | V _{DDQ} | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | V _{DDQ} | V _{REF} | ZQ |
| J | D31 | Q31 | D23 | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | D12 | Q4 | D4 |
| K | Q32 | D32 | Q23 | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | Q12 | D3 | Q3 |
| L | Q33 | Q24 | D24 | V _{DDQ} | V _{SS} | V _{SS} | V _{SS} | V _{DDQ} | D11 | Q11 | Q2 |
| M | D33 | Q34 | D25 | V _{SS} | V _{SS} | V _{SS} | V _{SS} | V _{SS} | D10 | Q1 | D2 |
| N | D34 | D26 | Q25 | V _{SS} | SA | SA | SA | V _{SS} | Q10 | D9 | D1 |
| P | Q35 | D35 | Q26 | SA | SA | C QVLD QVLD | SA | SA | Q9 | D0 | Q0 |
| R | TDO | TCK | SA | SA | SA | /C NC ODT | SA | SA | SA | TMS | TDI |

(Top View)

Top ←R1Q3A7236
 Mid ←R1QA(G)A7236
 Bottom ←R1QD(K)A7236

- Notes: 1. Address expansion order for future higher density SRAMs: 10A → 2A → 7A → 5B.
 2. NC pins can be left floating or connected to 0V ~ V_{DDQ}.

R1Q3A7218 (Top) / R1QA(G)A7218 (Mid) / R1QD(K)A7218 (Bottom)

| | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 |
|---|-------|------------------|------------------|------------------|-----------------|-------------------|-----------------|------------------|------------------|------------------|-----|
| A | /CQ | NC | SA | /W | /BW1 | /K | NC | /R | SA | SA | CQ |
| B | NC | Q9 | D9 | SA | NC | K | /BW0 | SA | NC | NC | Q8 |
| C | NC | NC | D10 | V _{SS} | SA | NC | SA | V _{SS} | NC | Q7 | D8 |
| D | NC | D11 | Q10 | V _{SS} | V _{SS} | V _{SS} | V _{SS} | V _{SS} | NC | NC | D7 |
| E | NC | NC | Q11 | V _{DDQ} | V _{SS} | V _{SS} | V _{SS} | V _{DDQ} | NC | D6 | Q6 |
| F | NC | Q12 | D12 | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | NC | NC | Q5 |
| G | NC | D13 | Q13 | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | NC | NC | D5 |
| H | /DOFF | V _{REF} | V _{DDQ} | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | V _{DDQ} | V _{REF} | ZQ |
| J | NC | NC | D14 | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | NC | Q4 | D4 |
| K | NC | NC | Q14 | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | NC | D3 | Q3 |
| L | NC | Q15 | D15 | V _{DDQ} | V _{SS} | V _{SS} | V _{SS} | V _{DDQ} | NC | NC | Q2 |
| M | NC | NC | D16 | V _{SS} | V _{SS} | V _{SS} | V _{SS} | V _{SS} | NC | Q1 | D2 |
| N | NC | D17 | Q16 | V _{SS} | SA | SA | SA | V _{SS} | NC | NC | D1 |
| P | NC | NC | Q17 | SA | SA | C QVLD QVLD | SA | SA | NC | D0 | Q0 |
| R | TDO | TCK | SA | SA | SA | /C NC ODT | SA | SA | SA | TMS | TDI |

(Top View)

- Notes: 1. Address expansion order for future higher density SRAMs: 10A → 2A → 7A → 5B.
 2. NC pins can be left floating or connected to 0V ~ V_{DDQ}.

Pin Arrangement

Just Reference

R1Q3A7209 (Top) / R1QA(G)A7209 (Mid) / R1QD(K)A7209 (Bottom)

| | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 |
|---|-------|------------------|------------------|------------------|-----------------|-------------------|-----------------|------------------|------------------|------------------|-----|
| A | /CQ | SA | SA | /W | NC | /K | NC | /R | SA | SA | CQ |
| B | NC | NC | NC | SA | NC | K | /BW | SA | NC | NC | Q4 |
| C | NC | NC | NC | V _{SS} | SA | NC | SA | V _{SS} | NC | NC | D4 |
| D | NC | D5 | NC | V _{SS} | V _{SS} | V _{SS} | V _{SS} | V _{SS} | NC | NC | NC |
| E | NC | NC | Q5 | V _{DDQ} | V _{SS} | V _{SS} | V _{SS} | V _{DDQ} | NC | D3 | Q3 |
| F | NC | NC | NC | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | NC | NC | NC |
| G | NC | D6 | Q6 | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | NC | NC | NC |
| H | /DOFF | V _{REF} | V _{DDQ} | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | V _{DDQ} | V _{REF} | ZQ |
| J | NC | NC | NC | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | NC | Q2 | D2 |
| K | NC | NC | NC | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | NC | NC | NC |
| L | NC | Q7 | D7 | V _{DDQ} | V _{SS} | V _{SS} | V _{SS} | V _{DDQ} | NC | NC | Q1 |
| M | NC | NC | NC | V _{SS} | V _{SS} | V _{SS} | V _{SS} | V _{SS} | NC | NC | D1 |
| N | NC | D8 | NC | V _{SS} | SA | SA | SA | V _{SS} | NC | NC | NC |
| P | NC | NC | Q8 | SA | SA | C QVLD QVLD | SA | SA | NC | D0 | Q0 |
| R | TDO | TCK | SA | SA | SA | /C NC ODT | SA | SA | SA | TMS | TDI |

(Top View)

- Notes: 1. Address expansion order for future higher density SRAMs: 10A → 2A → 7A → 5B.
 2. NC pins can be left floating or connected to 0V ~ V_{DDQ}.

Pin Descriptions

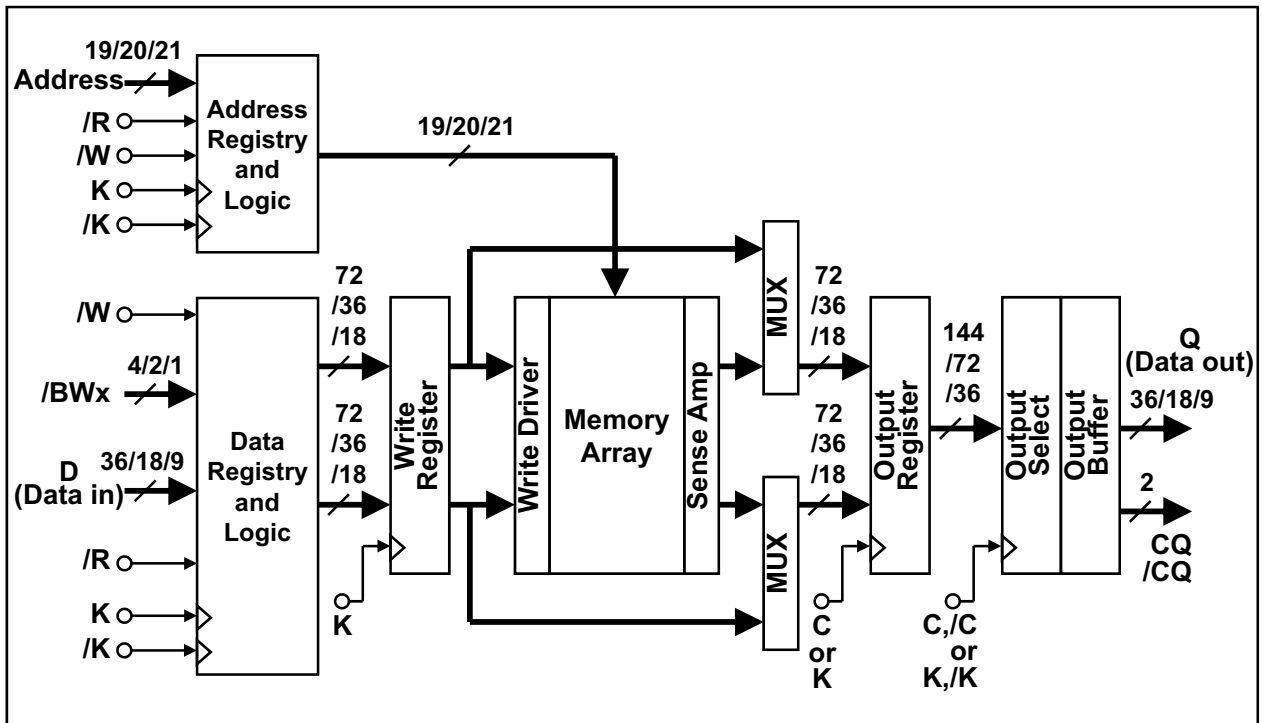
| Name | I/O type | Descriptions | Notes |
|--------------------|----------|--|-------|
| SA | Input | Synchronous address inputs: These inputs are registered and must meet the setup and hold times around the rising edge of K. All transactions operate on a burst-of-four words (two clock periods of bus activity). These inputs are ignored when device is deselected. | |
| /R | Input | Synchronous read: When low, this input causes the address inputs to be registered and a READ cycle to be initiated. This input must meet setup and hold times around the rising edge of K, and is ignored on the subsequent rising edge of K. | |
| /W | Input | Synchronous write: When low, this input causes the address inputs to be registered and a WRITE cycle to be initiated. This input must meet setup and hold times around the rising edge of K, and is ignored on the subsequent rising edge of K. | |
| /BW _x | Input | Synchronous byte writes: When low, these inputs cause their respective byte to be registered and written during WRITE cycles. These signals are sampled on the same edge as the corresponding data and must meet setup and hold times around the rising edges of K and /K for each of the two rising edges comprising the WRITE cycle. See Byte Write Truth Table for signal to data relationship. | |
| K, /K | Input | Input clock: This input clock pair registers address and control inputs on the rising edge of K, and registers data on the rising edge of K and the rising edge of /K. /K is ideally 180 degrees out of phase with K. All synchronous inputs must meet setup and hold times around the clock rising edges. These balls cannot remain V _{REF} level. | |
| C, /C (II only) | Input | Output clock: This clock pair provides a user-controlled means of tuning device output data. The rising edge of /C is used as the output timing reference for the first and third output data. The rising edge of C is used as the output timing reference for second and fourth output data. Ideally, /C is 180 degrees out of phase with C. C and /C may be tied high to force the use of K and /K as the output reference clocks instead of having to provide C and /C clocks. If tied high, C and /C must remain high and not to be toggled during device operation. These balls cannot remain V _{REF} level. | 1 |
| /DOFF | Input | DLL/PLL disable: When low, this input causes the DLL/PLL to be bypassed for stable, low frequency operation. | |
| TMS TDI | Input | IEEE1149.1 test inputs: 1.8 V I/O levels. These balls may be left not connected if the JTAG function is not used in the circuit. | |
| TCK | Input | IEEE1149.1 clock input: 1.8 V I/O levels. This ball must be tied to V _{SS} if the JTAG function is not used in the circuit. | |

Notes:

1. R1Q2, R1Q3, R1Q4, R1Q5, R1Q6 series have C and /C pins. R1QA, R1QB, R1QC, R1QD, R1QE, R1QF, R1QG, R1QH, R1QJ, R1QK, R1QL, R1QM, R1QN, R1QP series do not have C, /C pins. In the series, K and /K are used as the output reference clocks instead of C and /C. Therefore, hereafter, C and /C represent K and /K in this document.

| Name | I/O type | Descriptions | Notes |
|--|----------|--|-------|
| ZQ | Input | Output impedance matching input: This input is used to tune the device outputs to the system data bus impedance. Q and CQ output impedance are set to $0.2 \times RQ$, where RQ is a resistor from this ball to ground. This ball can be connected directly to V_{DDQ} , which enables the minimum impedance mode. This ball cannot be connected directly to V_{SS} or left unconnected. In ODT (On Die Termination) enable devices, the ODT termination values tracks the value of RQ. The ODT range is selected by ODT control input. | |
| ODT (II+ only) | Input | ODT control: When low ; [Option 1] Low range mode is selected. The impedance range is between 52Ω and 105Ω (Thevenin equivalent), which follows $0.3 \times RQ$ for $175 \Omega \leq RQ \leq 350 \Omega$. [Option 2] ODT is disabled. When high ; High range mode is selected. The impedance range is between 105Ω and 150Ω (Thevenin equivalent), which follows $0.6 \times RQ$ for $175 \Omega \leq RQ \leq 250 \Omega$. When floating ; [Option 1] High range mode is selected. [Option 2] ODT is disabled. | 1 |
| D_0 to D_n | Input | Synchronous data inputs: Input data must meet setup and hold times around the rising edges of K and /K during WRITE operations. See Pin Arrangement figures for ball site location of individual signals. The $\times 9$ device uses $D_0 \sim D_8$. $D_9 \sim D_{35}$ should be treated as NC pin. The $\times 18$ device uses $D_0 \sim D_{17}$. $D_{18} \sim D_{35}$ should be treated as NC pin. The $\times 36$ device uses $D_0 \sim D_{35}$. | |
| CQ, /CQ | Output | Synchronous echo clock outputs: The edges of these outputs are tightly matched to the synchronous data outputs and can be used as a data valid indication. These signals run freely and do not stop when Q tri-states. | |
| TDO | Output | IEEE 1149.1 test output: 1.8 V I/O level. | |
| Q_0 to Q_n | Output | Synchronous data outputs: Output data is synchronized to the respective C and /C, or to the respective K and /K if C and /C are tied high. This bus operates in response to /R commands. See Pin Arrangement figures for ball site location of individual signals. The $\times 9$ device uses $Q_0 \sim Q_8$. $Q_9 \sim Q_{35}$ should be treated as NC pin. The $\times 18$ device uses $Q_0 \sim Q_{17}$. $Q_{18} \sim Q_{35}$ should be treated as NC pin. The $\times 36$ device uses $Q_0 \sim Q_{35}$. | |
| QVLD (II+ only) | Output | Valid output indicator: The Q Valid indicates valid output data. QVLD is edge aligned with CQ and /CQ. | |
| V_{DD} | Supply | Power supply: 1.8 V nominal. See DC Characteristics and Operating Conditions for range. | 2 |
| V_{DDQ} | Supply | Power supply: Isolated output buffer supply. Nominally 1.5 V. See DC Characteristics and Operating Conditions for range. | 2 |
| V_{SS} | Supply | Power supply: Ground. | 2 |
| V_{REF} | — | HSTL input reference voltage: Nominally $V_{DDQ}/2$, but may be adjusted to improve system noise margin. Provides a reference voltage for the HSTL input buffers. | |
| NC | — | No connect: These pins can be left floating or connected to $0V \sim V_{DDQ}$. | |
| Notes: | | | |
| 1. Renesas status: Option 1 = Available, Option 2 = Possible. | | | |
| 2. All power supply and ground balls must be connected for proper operation of the device. | | | |

Block Diagram (R1QxA7236 / R1QxA7218 / R1QxA7209, x=3,A,D,G,K)



Notes

1. C and /C pins do not exist in II+ series parts.

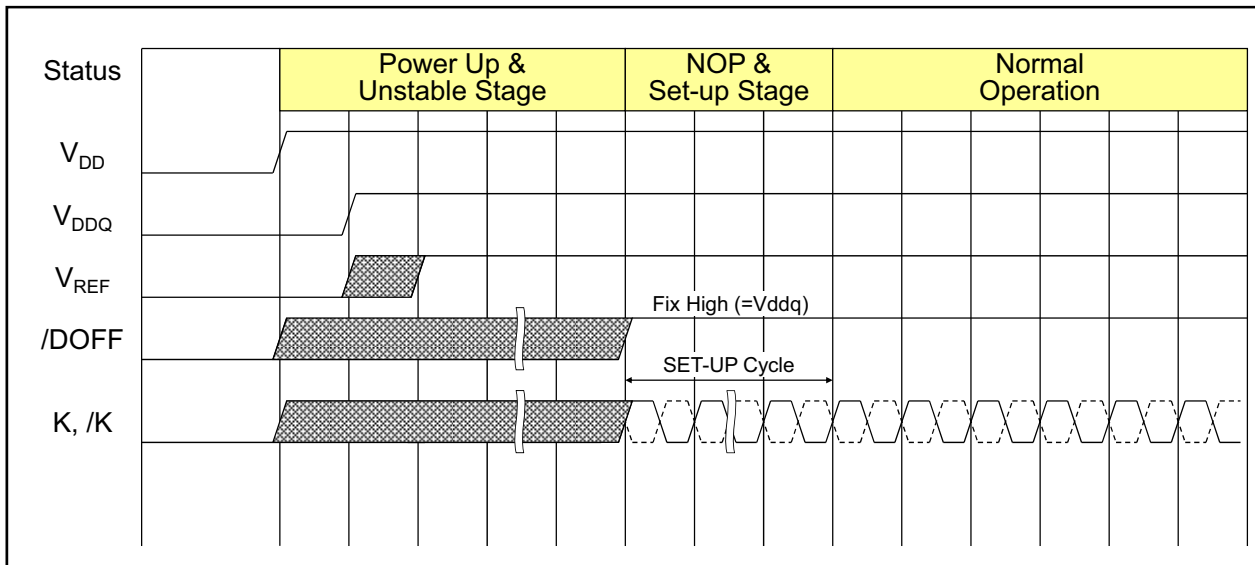
General Description

Power-up and Initialization Sequence

- V_{DD} must be stable before K, /K clocks are applied.
- Recommended voltage application sequence : $V_{SS} \rightarrow V_{DD} \rightarrow V_{DDQ} \& V_{REF} \rightarrow V_{IN}$. (0 V to V_{DD} , $V_{DDQ} < 200$ ms)
- Apply V_{REF} after V_{DDQ} or at the same time as V_{DDQ} .
- Then execute either one of the following three sequences.

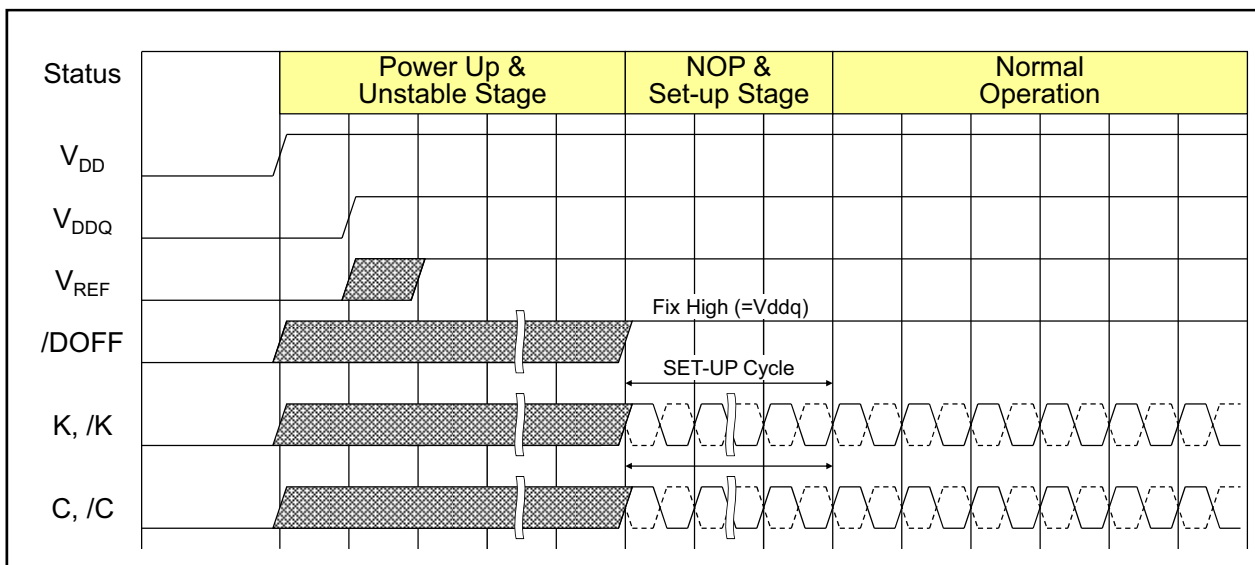
1. Single Clock Mode (C and /C tied high)

- Drive /DOFF high (/DOFF can be tied high from the start).
- Then provide stable clocks (K, /K) for at least 1024 cycles (II series) or 20 us (II+ series).
These meet the QDR common specification of 20 us.
- When the operating frequency is less than 180 MHz, 2048 cycles are required (II series).



2. Double Clock Mode (C and /C control outputs) (II series only)

- Drive /DOFF high (/DOFF can be tied high from the start)
- Then provide stable clocks (K, /K, C, /C) for at least 1024 cycles (II series).
This meets the QDR common specification of 20 us.
- When the operating frequency is less than 180 MHz, 2048 cycles are required (II series).



3. DLL/PLL Off Mode (/DOFF tied low)

- In the "NOP and setup stage", provide stable clocks (K, /K) for at least 1024 cycles (II series) or 20 us (II+ series). These meet the QDR common specification of 20 us.

DLL/PLL Constraints

1. DLL/PLL uses K clock as its synchronizing input. The input should have low phase jitter which is specified as $t_{KC \text{ var}}$.
2. The lower end of the frequency at which the DLL/PLL can operate is 120 MHz.
(Please refer to AC Characteristics table for detail.)
3. When the operating frequency is changed or /DOFF level is changed, setup cycles are required again.

Programmable Output Impedance

1. Output buffer impedance can be programmed by terminating the ZQ ball to V_{SS} through a precision resistor (RQ). The value of RQ is five times the output impedance desired. The allowable range of RQ to guarantee impedance matching with a tolerance of 15% is 250 Ω typical. The total external capacitance of ZQ ball must be less than 7.5 pF.

K Truth Table

| Operation | K | /R | /W | D or Q | | | | | |
|---|----------|---------|----------|---------------------|----------|----------|----------|----------|----------|
| Write Cycle: Load address, input write data on two consecutive K and /K rising edges | ↑ | H*7 | L*8 | Data in | | | | | |
| | | | | Input data | D(A+0) | D(A+1) | D(A+2) | D(A+3) | |
| | | | | Input clock | K(t+1)↑ | /K(t+1)↑ | K(t+2)↑ | /K(t+2)↑ | |
| Read Cycle: Load address, output read data on two consecutive C and /C rising edges | ↑ | L*8 | × | Data out | | | | | |
| | | | | Output data | Q(A+0) | Q(A+1) | Q(A+2) | Q(A+3) | |
| | | | | Input clock for Q | RL*9=1.5 | /C(t+1)↑ | C(t+2)↑ | /C(t+2)↑ | C(t+3)↑ |
| | | | | | RL=2.0 | C(t+2)↑ | /C(t+2)↑ | C(t+3)↑ | /C(t+3)↑ |
| RL=2.5 | /C(t+2)↑ | C(t+3)↑ | /C(t+3)↑ | | C(t+4)↑ | | | | |
| NOP (No operation) | ↑ | H | H | D = × or Q = High-Z | | | | | |
| Standby (Clock stopped) | Stopped | × | × | Previous state | | | | | |

Notes:

1. H: high level, L: low level, ×: don't care, ↑: rising edge.
2. Data inputs are registered at K and /K rising edges. Data outputs are delivered at C and /C rising edges, except if C and /C are high, then data outputs are delivered at K and /K rising edges.
3. /R and /W must meet setup/hold times around the rising edges (low to high) of K and are registered at the rising edge of K.
4. This device contains circuitry that will ensure the outputs will be in high-Z during power-up.
5. Refer to state diagram and timing diagrams for clarification.
6. When clocks are stopped, the following cases are recommended; the case of K = low, /K = high, C = low and /C = high, or the case of K = high, /K = low, C = high and /C = low. This condition is not essential, but permits most rapid restart by overcoming transmission line charging symmetrically.
7. If this signal was low to initiate the previous cycle, this signal becomes a "don't care" for this operation; however, it is strongly recommended that this signal be brought high, as shown in the truth table.
8. This signal was high on previous K clock rising edge. Initiating consecutive READ or WRITE operations on consecutive K clock rising edges is not permitted. The device will ignore the second request.
9. RL = Read Latency (unit = cycle).

Byte Write Truth Table (x 36)

| Operation | K | /K | /BW0 | /BW1 | /BW2 | /BW3 |
|------------------|---|----|------|------|------|------|
| Write D0 to D35 | ↑ | - | L | L | L | L |
| | - | ↑ | L | L | L | L |
| Write D0 to D8 | ↑ | - | L | H | H | H |
| | - | ↑ | L | H | H | H |
| Write D9 to D17 | ↑ | - | H | L | H | H |
| | - | ↑ | H | L | H | H |
| Write D18 to D26 | ↑ | - | H | H | L | H |
| | - | ↑ | H | H | L | H |
| Write D27 to D35 | ↑ | - | H | H | H | L |
| | - | ↑ | H | H | H | L |
| Write nothing | ↑ | - | H | H | H | H |
| | - | ↑ | H | H | H | H |

Notes:

1. H: high level, L: low level, ↑: rising edge.
2. Assumes a WRITE cycle was initiated. /BWx can be altered for any portion of the BURST WRITE operation provided that the setup and hold requirements are satisfied.

Byte Write Truth Table (x 18)

| Operation | K | /K | /BW0 | /BW1 |
|-----------------|---|----|------|------|
| Write D0 to D17 | ↑ | - | L | L |
| | - | ↑ | L | L |
| Write D0 to D8 | ↑ | - | L | H |
| | - | ↑ | L | H |
| Write D9 to D17 | ↑ | - | H | L |
| | - | ↑ | H | L |
| Write nothing | ↑ | - | H | H |
| | - | ↑ | H | H |

Notes:

1. H: high level, L: low level, ↑: rising edge.
2. Assumes a WRITE cycle was initiated. /BWx can be altered for any portion of the BURST WRITE operation provided that the setup and hold requirements are satisfied.

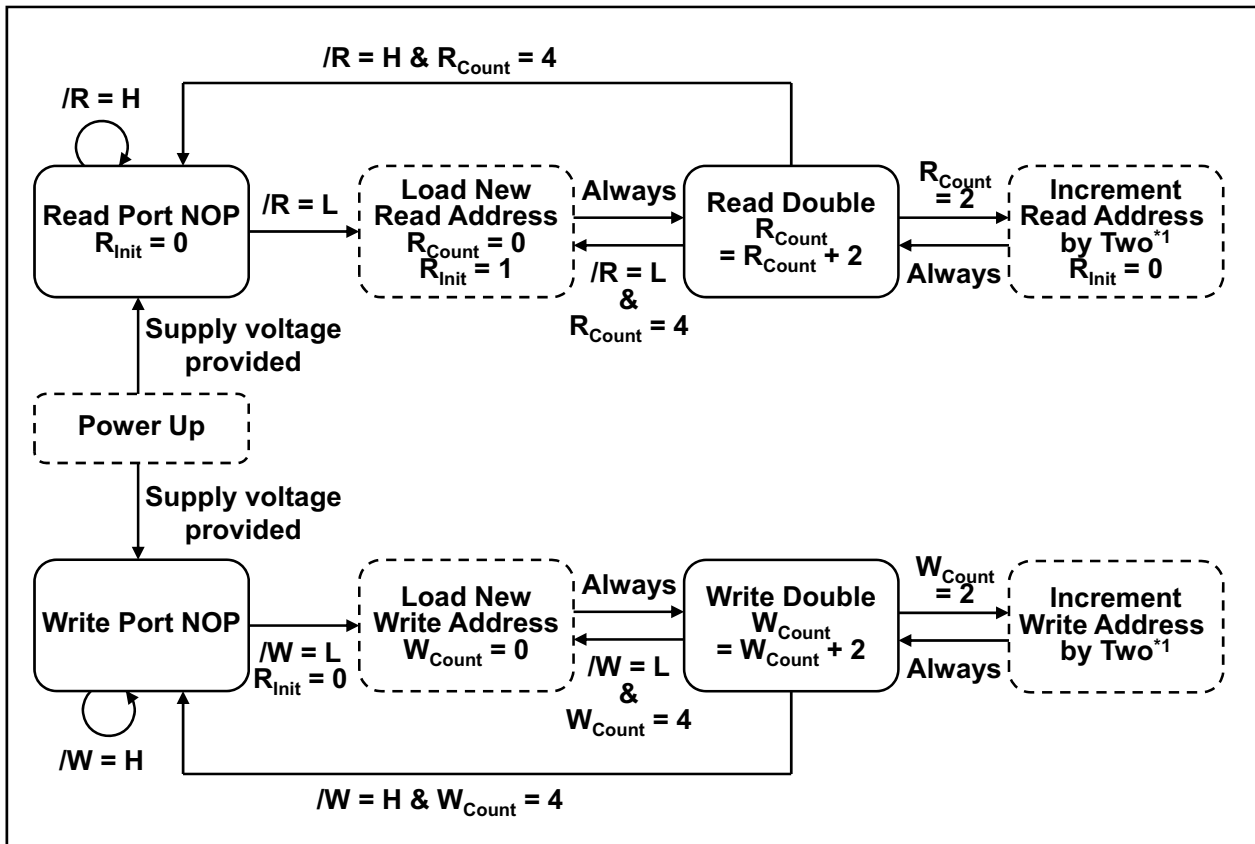
Byte Write Truth Table (x 9) Just Reference except R1Q2A**09 series

| Operation | K | /K | /BW |
|----------------|---|----|-----|
| Write D0 to D8 | ↑ | - | L |
| | - | ↑ | L |
| Write nothing | ↑ | - | H |
| | - | ↑ | H |

Notes:

1. H: high level, L: low level, ↑: rising edge.
2. Assumes a WRITE cycle was initiated. /BWx can be altered for any portion of the BURST WRITE operation provided that the setup and hold requirements are satisfied.

Bus Cycle State Diagram



Notes:

1. The address is concatenated with two additional internal LSBs to facilitate burst operation. The address order is always fixed as: $xxx\dots xxx+0$, $xxx\dots xxx+1$, $xxx\dots xxx+2$, $xxx\dots xxx+3$. Bus cycle is terminated at the end of this sequence (burst count = 4).
2. Read and write state machines can be active simultaneously. Read and write cannot be simultaneously initiated. Read takes precedence.
3. State machine control timing sequence is controlled by K.

Absolute Maximum Ratings

| Parameter | Symbol | Rating | Unit | Notes |
|---------------------------|-----------|---|------|-------|
| Input voltage on any ball | V_{IN} | -0.5 to $V_{DD} + 0.5$ (2.5 V max.) | V | 1, 4 |
| Input/output voltage | V_{IO} | -0.5 to $V_{DDQ} + 0.5$ (2.5 V max.) | V | 1, 4 |
| Core supply voltage | V_{DD} | -0.5 to 2.5 | V | 1, 4 |
| Output supply voltage | V_{DDQ} | -0.5 to V_{DD} | V | 1, 4 |
| Junction temperature | T_j | +125 (max) | °C | 5 |
| Storage temperature | T_{STG} | -55 to +125 | °C | |

Notes:

- All voltage is referenced to V_{SS} .
- Permanent device damage may occur if Absolute Maximum Ratings are exceeded. Functional operation should be restricted the Operation Conditions. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.
- These CMOS memory circuits have been designed to meet the DC and AC specifications shown in the tables after thermal equilibrium has been established.
- The following supply voltage application sequence is recommended: V_{SS} , V_{DD} , V_{DDQ} , V_{REF} then V_{IN} . Remember, according to the Absolute Maximum Ratings table, V_{DDQ} is not to exceed 2.5 V, whatever the instantaneous value of V_{DDQ} .
- Some method of cooling or airflow should be considered in the system. (Especially for high frequency or ODT parts)

Recommended DC Operating Conditions

| Parameter | Symbol | Min | Typ | Max | Unit | Notes |
|--------------------------------|--------------|-----------------|------|-----------------|------|---------|
| Power supply voltage -- core | V_{DD} | 1.7 | 1.8 | 1.9 | V | 1 |
| Power supply voltage -- I/O | V_{DDQ} | 1.4 | 1.5 | V_{DD} | V | 1, 2 |
| Input reference voltage -- I/O | V_{REF} | 0.68 | 0.75 | 0.95 | V | 3 |
| Input high voltage | $V_{IH(DC)}$ | $V_{REF} + 0.1$ | — | $V_{DDQ} + 0.3$ | V | 1, 4, 5 |
| Input low voltage | $V_{IL(DC)}$ | -0.3 | — | $V_{REF} - 0.1$ | V | 1, 4, 5 |

Notes:

- At power-up, V_{DD} and V_{DDQ} are assumed to be a linear ramp from 0V to V_{DD} (min.) or V_{DDQ} (min.) within 200ms. During this time $V_{DDQ} < V_{DD}$ and $V_{IH} < V_{DDQ}$. During normal operation, V_{DDQ} must not exceed V_{DD} .
- Please pay attention to T_j not to exceed the temperature shown in the absolute maximum ratings table due to current from V_{DDQ} .
- Peak to peak AC component superimposed on V_{REF} may not exceed 5% of V_{REF} .
- These are DC test criteria. The AC V_{IH} / V_{IL} levels are defined separately to measure timing parameters.
- Overshoot: $V_{IH(AC)} \leq V_{DDQ} + 0.5$ V for $t \leq t_{KHKH}/2$
Undershoot: $V_{IL(AC)} \geq -0.5$ V for $t \leq t_{KHKH}/2$
During normal operation, $V_{IH(DC)}$ must not exceed V_{DDQ} and $V_{IL(DC)}$ must not be lower than V_{SS} .

DC Characteristics

(Ta = 0 ~ +70°C @ R1Q*A*****BB-**R** series, Ta = -40 ~ +85°C @ R1Q*A*****BB-**I** series)
 (V_{DD} = 1.8V ±0.1V, V_{DDQ} = 1.5V, V_{REF} = 0.75V)

Operating Supply Current (Write / Read)

Symbol = I_{DD}. Unit = mA. See Notes 1, 2 and 3 in the page after next.

| No | Product Type | Burst Length | Latency (Cycle) | ODT | Organi- zation | Frequency (max) (MHz) | QDR II+ / DDR II+ | | | | | | QDR II / DDR II | | | | | | |
|---------------|--------------|--------------|-----------------|---------------------|---------------------|-----------------------|-----------------------|------|------|------|-----|-----|-----------------|------|------|------|------|------|------|
| | | | | | | | 533 | 500 | 450 | 400 | 375 | 333 | 333 | 300 | 250 | 200 | | | |
| | | | | | | | Cycle Time (min) (ns) | | | | | | 1.875 | 2.00 | 2.22 | 2.50 | 2.66 | 3.00 | 3.00 |
| Part Number ↓ | | yy → | | -19 | -20 | -22 | -25 | -27 | -30 | -30 | -33 | -40 | -50 | | | | | | |
| 1 | QDRII | B2 | 1.5 | No | x 9 | R1Q 2 A72 09 ABv-yy | | | | | | | | | | 760 | 670 | | |
| 2 | | | | | x18 | R1Q 2 A72 18 ABv-yy | | | | | | | | | | | 890 | 780 | |
| 3 | | | | | x36 | R1Q 2 A72 36 ABv-yy | | | | | | | | | | | 950 | 830 | |
| 5 | B4 | x18 | | | R1Q 3 A72 18 ABv-yy | | | | | | | 880 | 820 | 730 | | | | | |
| 6 | | x36 | | | R1Q 3 A72 36 ABv-yy | | | | | | | 910 | 850 | 750 | | | | | |
| 8 | | x18 | | | R1Q 4 A72 18 ABv-yy | | | | | | | 750 | 700 | 630 | | | | | |
| 9 | DDRII | B2 | x36 | R1Q 4 A72 36 ABv-yy | | | | | | 810 | 760 | 680 | | | | | | | |
| 11 | | | B4 | x18 | R1Q 5 A72 18 ABv-yy | | | | | | 660 | 630 | 590 | | | | | | |
| 12 | | | | x36 | R1Q 5 A72 36 ABv-yy | | | | | | 700 | 670 | 630 | | | | | | |
| 14 | DDRII SIO | B2 | x18 | R1Q 6 A72 18 ABv-yy | | | | | | 750 | 700 | 630 | | | | | | | |
| 15 | | | x36 | R1Q 6 A72 36 ABv-yy | | | | | | | 810 | 760 | 680 | | | | | | |
| 17 | QDRII+ | B4 | 2.5 | No | x18 | R1Q A A72 18 ABv-yy | 1220 | 1160 | 1070 | | | | | | | | | | |
| 18 | | | | | x36 | R1Q A A72 36 ABv-yy | 1280 | 1220 | 1130 | | | | | | | | | | |
| 20 | DDRII+ | B2 | | | x18 | R1Q B A72 18 ABv-yy | 1030 | 990 | 920 | | | | | | | | | | |
| 21 | | | | | x36 | R1Q B A72 36 ABv-yy | 1110 | 1060 | 990 | | | | | | | | | | |
| 23 | | B4 | | | x18 | R1Q C A72 18 ABv-yy | 820 | 790 | 750 | | | | | | | | | | |
| 24 | | | | | x36 | R1Q C A72 36 ABv-yy | 880 | 850 | 800 | | | | | | | | | | |
| 26 | QDRII+ | B4 | x18 | R1Q D A72 18 ABv-yy | 1220 | 1160 | 1070 | | | | | | | | | | | | |
| 27 | | | x36 | R1Q D A72 36 ABv-yy | 1280 | 1220 | 1130 | | | | | | | | | | | | |
| 29 | DDRII+ | B2 | x18 | R1Q E A72 18 ABv-yy | 1030 | 990 | 920 | | | | | | | | | | | | |
| 30 | | | x36 | R1Q E A72 36 ABv-yy | 1110 | 1060 | 990 | | | | | | | | | | | | |
| 32 | | B4 | x18 | R1Q F A72 18 ABv-yy | 820 | 790 | 750 | | | | | | | | | | | | |
| 33 | | | x36 | R1Q F A72 36 ABv-yy | 880 | 850 | 800 | | | | | | | | | | | | |
| 35 | QDRII+ | B4 | 2.0 | No | x18 | R1Q G A72 18 ABv-yy | | | | 980 | | | | | | | | | |
| 36 | | | | | x36 | R1Q G A72 36 ABv-yy | | | | 1060 | | | | | | | | | |
| 38 | DDRII+ | B2 | | | x18 | R1Q H A72 18 ABv-yy | | | | 850 | | | | | | | | | |
| 39 | | | | | x36 | R1Q H A72 36 ABv-yy | | | | 910 | | | | | | | | | |
| 41 | | B4 | | | x18 | R1Q J A72 18 ABv-yy | | | | 710 | | | | | | | | | |
| 42 | | | | | x36 | R1Q J A72 36 ABv-yy | | | | 760 | | | | | | | | | |
| 44 | QDRII+ | B4 | x18 | R1Q K A72 18 ABv-yy | | | | 980 | | | | | | | | | | | |
| 45 | | | x36 | R1Q K A72 36 ABv-yy | | | | 1060 | | | | | | | | | | | |
| 47 | DDRII+ | B2 | x18 | R1Q L A72 18 ABv-yy | | | | 850 | | | | | | | | | | | |
| 48 | | | x36 | R1Q L A72 36 ABv-yy | | | | 910 | | | | | | | | | | | |
| 50 | | B4 | x18 | R1Q M A72 18 ABv-yy | | | | 710 | | | | | | | | | | | |
| 51 | | | x36 | R1Q M A72 36 ABv-yy | | | | 760 | | | | | | | | | | | |

Notes:

- "v" represents the package size. If "v" = "G" then size is 15 x 17 mm, and if "v" = "B" then 13 x 15 mm.
- "yy" represents the speed bin. "R1QAA7236ABG-20" can operate at 500 MHz(max) of frequency, for example.

Standby Supply Current (NOP)

Symbol = I_{SB1} . Unit = mA. See Notes 2, 4 and 5 in the next page.

| No | Product Type | Burst Length | Latency (Cycle) | ODT | Organi- zation | Frequency (max) (MHz) | QDR II+ / DDR II+ | | | | | | QDR II / DDR II | | | | | | | | | |
|----|--------------|--------------|-----------------|---------------------|---------------------|-----------------------|-----------------------|------|-----|-----|-----|-----|-----------------|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| | | | | | | | Cycle Time (min) (ns) | | | | | | 533 | 500 | 450 | 400 | 375 | 333 | 333 | 300 | 250 | 200 |
| | | | | | | | Part Number ↓ | yy → | -19 | -20 | -22 | -25 | -27 | -30 | -30 | -33 | -40 | -50 | | | | |
| 1 | QDRII | B2 | 1.5 | No | x 9 | R1Q 2 A72 09 ABv-yy | | | | | | | | | | | 570 | 510 | | | | |
| 2 | | | | | x18 | R1Q 2 A72 18 ABv-yy | | | | | | | | | | | | | 670 | 600 | | |
| 3 | | | | | x36 | R1Q 2 A72 36 ABv-yy | | | | | | | | | | | | | | 710 | 630 | |
| 5 | B4 | x18 | | | R1Q 3 A72 18 ABv-yy | | | | | | | | | 630 | 590 | | | | 520 | | | |
| 6 | | x36 | | | R1Q 3 A72 36 ABv-yy | | | | | | | | | 650 | 610 | | | | 540 | | | |
| 8 | | x18 | | | R1Q 4 A72 18 ABv-yy | | | | | | | | | 650 | 610 | | | | 560 | | | |
| 9 | DDRII | B2 | x36 | R1Q 4 A72 36 ABv-yy | | | | | | | | 710 | 670 | | | | 610 | | | | | |
| 11 | | | B4 | x18 | R1Q 5 A72 18 ABv-yy | | | | | | | | 540 | 510 | | | | 480 | | | | |
| 12 | | | | x36 | R1Q 5 A72 36 ABv-yy | | | | | | | | | 570 | 540 | | | | 500 | | | |
| 14 | DDRII SIO | B2 | x18 | R1Q 6 A72 18 ABv-yy | | | | | | | | 650 | 610 | | | | 560 | | | | | |
| 15 | | | x36 | R1Q 6 A72 36 ABv-yy | | | | | | | | | 710 | 670 | | | | 610 | | | | |
| 17 | QDRII+ | B4 | 2.5 | No | x18 | R1Q A A72 18 ABv-yy | 870 | 830 | 780 | | | | | | | | | | | | | |
| 18 | | | | | x36 | R1Q A A72 36 ABv-yy | 910 | 870 | 810 | | | | | | | | | | | | | |
| 20 | DDRII+ | B2 | | | x18 | R1Q B A72 18 ABv-yy | 870 | 840 | 780 | | | | | | | | | | | | | |
| 21 | | | | | x36 | R1Q B A72 36 ABv-yy | 960 | 920 | 860 | | | | | | | | | | | | | |
| 23 | | B4 | | | x18 | R1Q C A72 18 ABv-yy | 690 | 660 | 630 | | | | | | | | | | | | | |
| 24 | | | | | x36 | R1Q C A72 36 ABv-yy | 730 | 710 | 670 | | | | | | | | | | | | | |
| 26 | QDRII+ | B4 | x18 | R1Q D A72 18 ABv-yy | 870 | 830 | 780 | | | | | | | | | | | | | | | |
| 27 | | | x36 | R1Q D A72 36 ABv-yy | 910 | 870 | 810 | | | | | | | | | | | | | | | |
| 29 | DDRII+ | B2 | x18 | R1Q E A72 18 ABv-yy | 870 | 840 | 780 | | | | | | | | | | | | | | | |
| 30 | | | x36 | R1Q E A72 36 ABv-yy | 960 | 920 | 860 | | | | | | | | | | | | | | | |
| 32 | | B4 | x18 | R1Q F A72 18 ABv-yy | 690 | 660 | 630 | | | | | | | | | | | | | | | |
| 33 | | | x36 | R1Q F A72 36 ABv-yy | 730 | 710 | 670 | | | | | | | | | | | | | | | |
| 35 | QDRII+ | B4 | x18 | R1Q G A72 18 ABv-yy | | | | 720 | | | | | | | | | | | | | | |
| 36 | | | x36 | R1Q G A72 36 ABv-yy | | | | 770 | | | | | | | | | | | | | | |
| 38 | DDRII+ | B2 | x18 | R1Q H A72 18 ABv-yy | | | | 720 | | | | | | | | | | | | | | |
| 39 | | | x36 | R1Q H A72 36 ABv-yy | | | | 790 | | | | | | | | | | | | | | |
| 41 | | B4 | x18 | R1Q J A72 18 ABv-yy | | | | 590 | | | | | | | | | | | | | | |
| 42 | | | x36 | R1Q J A72 36 ABv-yy | | | | 630 | | | | | | | | | | | | | | |
| 44 | QDRII+ | B4 | x18 | R1Q K A72 18 ABv-yy | | | | 720 | | | | | | | | | | | | | | |
| 45 | | | x36 | R1Q K A72 36 ABv-yy | | | | 770 | | | | | | | | | | | | | | |
| 47 | DDRII+ | B2 | x18 | R1Q L A72 18 ABv-yy | | | | 720 | | | | | | | | | | | | | | |
| 48 | | | x36 | R1Q L A72 36 ABv-yy | | | | 790 | | | | | | | | | | | | | | |
| 50 | | B4 | x18 | R1Q M A72 18 ABv-yy | | | | 590 | | | | | | | | | | | | | | |
| 51 | | | x36 | R1Q M A72 36 ABv-yy | | | | 630 | | | | | | | | | | | | | | |

Notes:

- "v" represents the package size. If "v" = "G" then size is 15 x 17 mm, and if "v" = "B" then 13 x 15 mm.
- "yy" represents the speed bin. "R1QAA7236ABG-20" can operate at 500 MHz(max) of frequency, for example.

Leakage Currents & Output Voltage

| Parameter | Symbol | Min | Max | Unit | Test condition | Notes |
|------------------------|-------------------|--------------------|--------------------|---------------|--------------------------------|-------|
| Input leakage current | I_{LI} | -2 | 2 | μA | | 10 |
| Output leakage current | I_{LO} | -5 | 5 | μA | | 11 |
| Output high voltage | V_{OH} (Low) | $V_{DDQ} - 0.2$ | V_{DDQ} | V | $ I_{OH} \leq 0.1 \text{ mA}$ | 8, 9 |
| | V_{OH} | $V_{DDQ}/2 - 0.12$ | $V_{DDQ}/2 + 0.12$ | V | Note 6 | 8, 9 |
| Output low voltage | V_{OL} (Low) | V_{SS} | 0.2 | V | $I_{OL} \leq 0.1 \text{ mA}$ | 8, 9 |
| | V_{OL} | $V_{DDQ}/2 - 0.12$ | $V_{DDQ}/2 + 0.12$ | V | Note 7 | 8, 9 |

Notes:

- All inputs (except ZQ, V_{REF}) are held at either V_{IH} or V_{IL} .
- $I_{OUT} = 0 \text{ mA}$. $V_{DD} = V_{DD} \text{ max}$, $t_{KHKH} = t_{KHKH} \text{ min}$.
- Operating supply currents (I_{DD}) are measured at 100% bus utilization. I_{DD} of QDR family is current of device with 100% write and 100% read cycle. I_{DD} of DDR family is current of device with 100% write cycle (if $I_{DD}(\text{Write}) > I_{DD}(\text{Read})$) or 100% read cycle (if $I_{DD}(\text{Write}) < I_{DD}(\text{Read})$).
- All address / data inputs are static at either $V_{IN} > V_{IH}$ or $V_{IN} < V_{IL}$.
- Reference value. (Condition = NOP currents are valid when entering NOP after all pending READ and WRITE cycles are completed.)
- Outputs are impedance-controlled. $|I_{OH}| = (V_{DDQ}/2)/(RQ/5)$ for values of $175 \Omega \leq RQ \leq 350 \Omega$.
- Outputs are impedance-controlled. $I_{OL} = (V_{DDQ}/2)/(RQ/5)$ for values of $175 \Omega \leq RQ \leq 350 \Omega$.
- AC load current is higher than the shown DC values. AC I/O curves are available upon request.
- HSTL outputs meet JEDEC HSTL Class I and Class II standards.
- $0 \leq V_{IN} \leq V_{DDQ}$ for all input balls (except V_{REF} , ZQ, TCK, TMS, TDI ball).
If R1QD, R1QE, R1QF, R1QK, R1QL, R1QM, R1QP series, balls with ODT do not follow this spec.
- $0 \leq V_{OUT} \leq V_{DDQ}$ (except TDO ball), output disabled.

Thermal Resistance

| Parameter | Symbol | Airflow | Typ | Unit | Test condition | Notes |
|---------------------|---------------|---------|------|------|------------------|-------|
| Junction to Ambient | θ_{JA} | 1 m/s | 11.0 | °C/W | EIA/JEDEC JESD51 | 1 |
| Junction to Case | θ_{JC} | - | 4.4 | | | |

Notes:

- These parameters are calculated under the condition. These are reference values.
- $T_j = T_a + \theta_{JA} \times P_d$
 $T_j = T_c + \theta_{JC} \times P_d$
 where
 T_j : junction temperature when the device has achieved a steady-state after application of P_d (°C)
 T_a : ambient temperature (°C)
 T_c : temperature of external surface of the package or case (°C)
 θ_{JA} : thermal resistance from junction-to-ambient (°C/W)
 θ_{JC} : thermal resistance from junction-to-case (package) (°C/W)
 P_d : power dissipation that produced change in junction temperature (W) (cf.JESD51-2A)

Capacitance

($T_a = +25^\circ\text{C}$, Frequency = 1.0MHz, $V_{DD} = 1.8\text{V}$, $V_{DDQ} = 1.5\text{V}$)

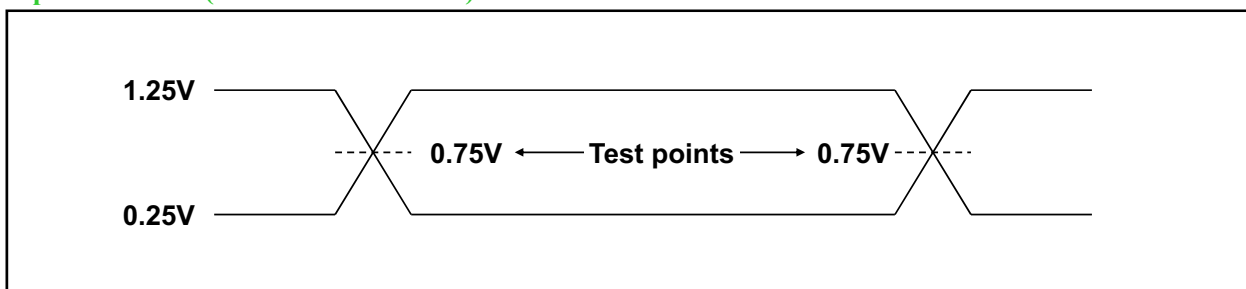
| Parameter | Symbol | Min | Typ | Max | Unit | Test condition | Notes |
|--|-----------|-----|-----|-----|------|-----------------------|-------|
| Input capacitance (SA, /R, /W, /BW, D(separate)) | C_{IN} | — | 4 | 5 | pF | $V_{IN} = 0\text{V}$ | 1, 2 |
| Clock input capacitance (K, /K, C, /C) | C_{CLK} | — | 4 | 5 | pF | $V_{CLK} = 0\text{V}$ | 1, 2 |
| Output capacitance (Q(separate), DQ(common), CQ, /CQ) | $C_{I/O}$ | — | 5 | 6 | pF | $V_{I/O} = 0\text{V}$ | 1, 2 |

Notes:

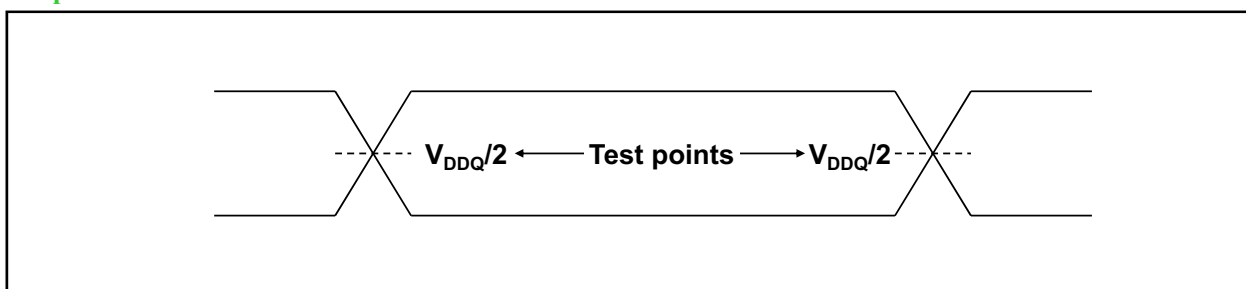
- These parameters are sampled and not 100% tested.
- Except JTAG (TCK, TMS, TDI, TDO) pins.

AC Test Conditions

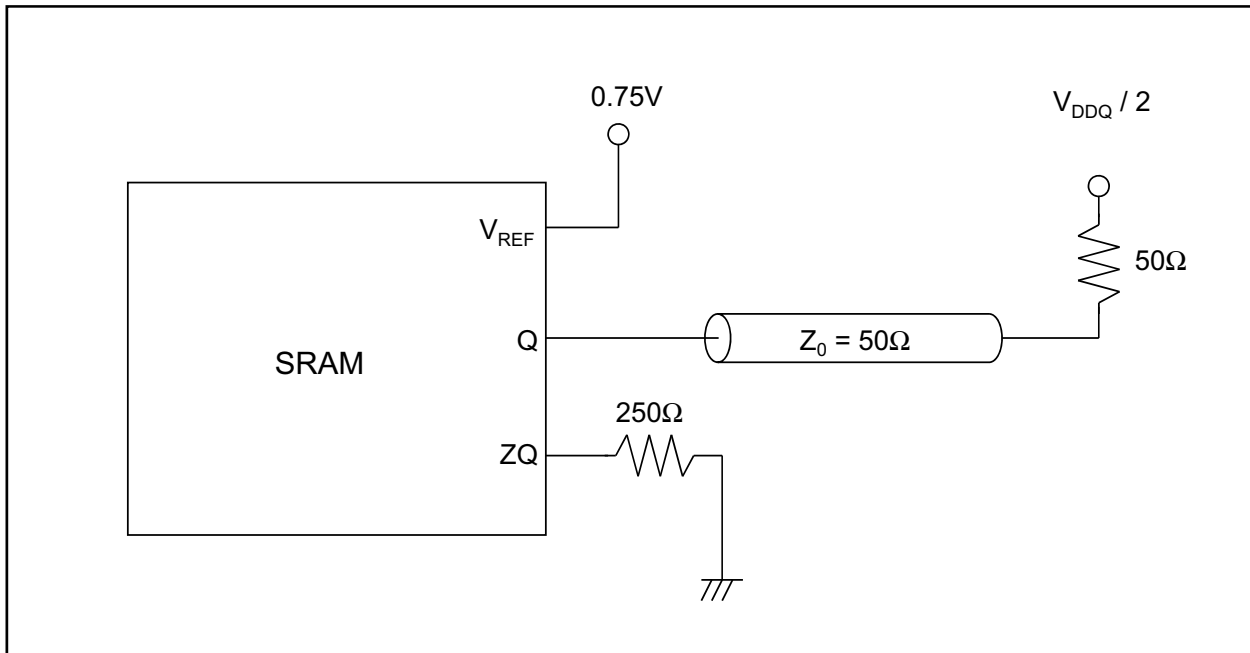
Input waveform (Rise/fall time $\leq 0.3\text{ ns}$)



Output waveform



Output load conditions



AC Operating Conditions

| Parameter | Symbol | Min | Typ | Max | Unit | Notes |
|--------------------|--------------|-----------------|-----|-----------------|------|------------|
| Input high voltage | $V_{IH(AC)}$ | $V_{REF} + 0.2$ | — | — | V | 1, 2, 3, 4 |
| Input low voltage | $V_{IL(AC)}$ | — | — | $V_{REF} - 0.2$ | V | 1, 2, 3, 4 |

Notes:

1. All voltages referenced to V_{SS} (GND).
During normal operation, V_{DDQ} must not exceed V_{DD} .
2. These conditions are for AC functions only, not for AC parameter test.
3. Overshoot: $V_{IH(AC)} \leq V_{DDQ} + 0.5\text{ V}$ for $t \leq t_{KHKH}/2$
Undershoot: $V_{IL(AC)} \geq -0.5\text{ V}$ for $t \leq t_{KHKH}/2$
Control input signals may not have pulse widths less than t_{KHKL} (min) or operate at cycle rates less than t_{KHKH} (min).
4. To maintain a valid level, the transitioning edge of the input must:
 - a. Sustain a constant slew rate from the current AC level through the target AC level, $V_{IL(AC)}$ or $V_{IH(AC)}$.
 - b. Reach at least the target AC level.
 - c. After the AC target level is reached, continue to maintain at least the target DC level, $V_{IL(DC)}$ or $V_{IH(DC)}$.

AC Characteristics (QDR-II, DDR-II series)

(Ta = 0 ~ +70°C @ R1Q*A*****BB-**R** series)

(Ta = -40 ~ +85°C @ R1Q*A*****BB-**I** series)

(V_{DD} = 1.8V ±0.1V, V_{DDQ} = 1.5V, V_{REF} = 0.75V)

| Parameter | Symbol | -30 | | -33 | | -40 | | -50 | | — | | — | | Unit | Notes |
|---|-----------------------|-------|------|-------|------|-------|------|-------|------|-----|-----|-----|-----|-------|---------|
| | | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max | | |
| Clock | | | | | | | | | | | | | | | |
| Average clock cycle time (K, /K, C, /C) | t _{KHKH} | 3.00 | 8.40 | 3.30 | 8.40 | 4.00 | 8.40 | 5.00 | 8.40 | — | — | — | — | ns | 8 |
| Clock high time (K, /K, C, /C) | t _{KHKL} | 1.20 | — | 1.32 | — | 1.60 | — | 2.00 | — | — | — | — | — | ns | |
| Clock low time (K, /K, C, /C) | t _{KLKH} | 1.20 | — | 1.32 | — | 1.60 | — | 2.00 | — | — | — | — | — | ns | |
| Clock to /clock (K to /K, C to /C) | t _{KH/KH} | 1.35 | — | 1.49 | — | 1.80 | — | 2.20 | — | — | — | — | — | ns | |
| /Clock to clock (/K to K, /C to C) | t _{/KHKH} | 1.35 | — | 1.49 | — | 1.80 | — | 2.20 | — | — | — | — | — | ns | |
| Clock to data clock (K to C, /K to /C) | t _{KHCH} | 0 | 1.35 | 0 | 1.49 | 0 | 1.80 | 0 | 2.20 | — | — | — | — | ns | |
| DLL/PLL Timing | | | | | | | | | | | | | | | |
| Clock phase jitter (K, /K, C, /C) | t _{KC var} | — | 0.20 | — | 0.20 | — | 0.20 | — | 0.20 | — | — | — | — | ns | 3 |
| Lock time (K, C) | t _{KC lock} | 1024 | — | 1024 | — | 1024 | — | 1024 | — | — | — | — | — | Cycle | 2 |
| K static to DLL/PLL reset | t _{KC reset} | 30 | — | 30 | — | 30 | — | 30 | — | — | — | — | — | ns | 7 |
| Output Times | | | | | | | | | | | | | | | |
| C, /C high to output valid | t _{CHQV} | — | 0.45 | — | 0.45 | — | 0.45 | — | 0.45 | — | — | — | — | ns | 9 |
| C, /C high to output hold | t _{CHQX} | -0.45 | — | -0.45 | — | -0.45 | — | -0.45 | — | — | — | — | — | ns | 9 |
| C, /C high to echo clock valid | t _{CHCQV} | — | 0.45 | — | 0.45 | — | 0.45 | — | 0.45 | — | — | — | — | ns | 9 |
| C, /C high to echo clock hold | t _{CHCQX} | -0.45 | — | -0.45 | — | -0.45 | — | -0.45 | — | — | — | — | — | ns | 9 |
| CQ, /CQ high to output valid | t _{CQHCV} | — | 0.25 | — | 0.27 | — | 0.30 | — | 0.35 | — | — | — | — | ns | 4, 7 |
| CQ, /CQ high to output hold | t _{CQHCV} | -0.25 | — | -0.27 | — | -0.30 | — | -0.35 | — | — | — | — | — | ns | 4, 7 |
| C, /C high to output high-Z | t _{CHQZ} | — | 0.45 | — | 0.45 | — | 0.45 | — | 0.45 | — | — | — | — | ns | 5, 6, 9 |
| C, /C high to output low-Z | t _{CHQX1} | -0.45 | — | -0.45 | — | -0.45 | — | -0.45 | — | — | — | — | — | ns | 5, 9 |
| — | — | — | — | — | — | — | — | — | — | — | — | — | — | — | — |

| Parameter | Symbol | -30 | | -33 | | -40 | | -50 | | — | | — | | Unit | Notes |
|---------------------------------------|---------------------------|------|-----|------|-----|------|-----|------|-----|-----|-----|-----|-----|------|-------|
| | | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max | | |
| Setup Times | | | | | | | | | | | | | | | |
| Address valid to K rising edge | t_{AVKH} for R1Q2 | — | — | — | — | 0.35 | — | 0.40 | — | — | — | — | — | ns | 1 |
| | t_{AVKH} for R1Q3/4/5/6 | 0.40 | — | 0.40 | — | 0.50 | — | 0.60 | — | — | — | — | — | | |
| Control inputs valid to K rising edge | t_{IVKH} for R1Q2 | — | — | — | — | 0.35 | — | 0.40 | — | — | — | — | ns | 1 | |
| | t_{IVKH} for R1Q3/4/5/6 | 0.40 | — | 0.40 | — | 0.50 | — | 0.60 | — | — | — | — | | | |
| Data-in valid to K, /K rising edge | t_{DVKH} | 0.28 | — | 0.30 | — | 0.35 | — | 0.40 | — | — | — | — | ns | 1 | |
| Hold Times | | | | | | | | | | | | | | | |
| K rising edge to address hold | t_{KHAX} for R1Q2 | — | — | — | — | 0.35 | — | 0.40 | — | — | — | — | ns | 1 | |
| | t_{KHAX} for R1Q3/4/5/6 | 0.40 | — | 0.40 | — | 0.50 | — | 0.60 | — | — | — | — | | | |
| K rising edge to control inputs hold | t_{KHIX} for R1Q2 | — | — | — | — | 0.35 | — | 0.40 | — | — | — | — | ns | 1 | |
| | t_{KHIX} for R1Q3/4/5/6 | 0.40 | — | 0.40 | — | 0.50 | — | 0.60 | — | — | — | — | | | |
| K, /K rising edge to data-in hold | t_{KHDX} | 0.28 | — | 0.30 | — | 0.35 | — | 0.40 | — | — | — | — | ns | 1 | |

Notes:

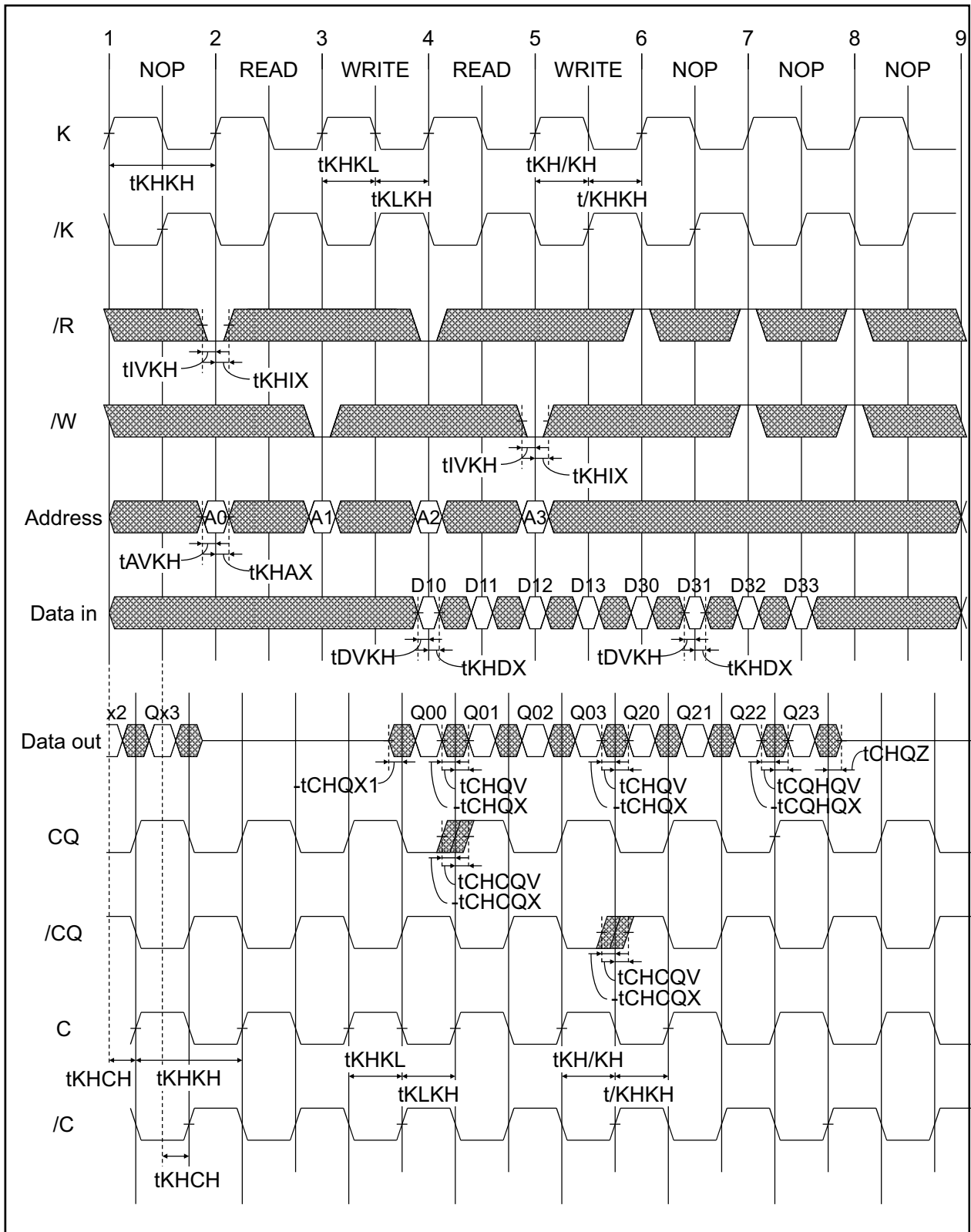
1. This is a synchronous device. All addresses, data and control lines must meet the specified setup and hold times for all latching clock edges.
2. V_{DD} and V_{DDQ} slew rate must be less than 0.1 V DC per 50 ns for DLL/PLL lock retention. DLL/PLL lock time begins once V_{DD} , V_{DDQ} and input clock are stable. It is recommended that the device is kept inactive during these cycles. This specification meets the QDR common spec. of 20 us.
3. Clock phase jitter is the variance from clock rising edge to the next expected clock rising edge.
4. Echo clock is very tightly controlled to data valid / data hold. By design, there is a ± 0.1 ns variation from echo clock to data. The datasheet parameters reflect tester guardbands and test setup variations.
5. Transitions are measured ± 100 mV from steady-state voltage.
6. At any given voltage and temperature t_{CHQZ} is less than t_{CHQX1} and t_{CHQV} .
7. These parameters are sampled.
8. When x18 and x36 configuration except QDRII-B2 are operated at less than 180MHz, DLL/PLL should be disabled (/DOFF=L). Please contact Renesas if these devices are always used at less than 180MHz with DLL/PLL operation.
9. t_{CHQV} , t_{CHQX} , t_{CHCQV} , t_{CHCQX} , t_{CHQZ} , t_{CHQX1} spec of R1Q3A and R1Q4A series is determined by the actual frequency regardless of Part Number (Marking Name). The following is the spec for the actual frequency.
 t_{CHQV} , t_{CHCQV} , t_{CHQZ} = 0.45 ns for ≥ 200 MHz and 0.50 ns for < 200 MHz
 t_{CHQX} , t_{CHCQX} , t_{CHQX1} = -0.45 ns for ≥ 200 MHz and -0.50 ns for < 200 MHz

Remarks:

1. Test conditions as specified with the output loading as shown in AC Test Conditions unless otherwise noted.
2. Control input signals may not be operated with pulse widths less than t_{KHKL} (min).
3. If C, /C are tied high, K, /K become the references for C, /C timing parameters.
4. V_{DDQ} is +1.5 V DC. V_{REF} is +0.75 V DC.
5. Control signals are /R, /W (QDR series), /LD, R-/W (DDR series), /BW, /BW0, /BW1, /BW2 and /BW3. Setup and hold times of /BWx signals must be the same as those of Data-in signals.

Timing Waveforms

Read and Write Timing (QDRII, B4, Read Latency = 1.5 cycle)



Notes:

1. Q00 refers to output from address A0+0. Q01 refers to output from the next internal burst address following A0, i.e., A0+1.
2. Outputs are disabled (high-Z) N clock cycle after the last read cycle. Here, N = Read Latency + Burst Length × 0.5.
3. In this example, if address A2 = A1, then data Q20 = D10, Q21 = D11. Write data is forwarded immediately as read results.
4. To control read and write operations, /BW signals must operate at the same timing as Data-in signals.

JTAG Specification

These products support a limited set of JTAG functions as in IEEE standard 1149.1.

Disabling the Test Access Port

It is possible to use this device without utilizing the TAP. To disable the TAP controller without interfering with normal operation of the device, TCK must be tied to V_{SS} to preclude mid level inputs.

TDI and TMS are internally pulled up and may be unconnected, or may be connected to VDD through a pull up resistor.

TDO should be left unconnected.

Test Access Port (TAP) Pins

| Symbol I/O | Pin assignments | Description | Notes |
|------------|-----------------|---|-------|
| TCK | 2R | Test clock input. All inputs are captured on the rising edge of TCK and all outputs propagate from the falling edge of TCK. | |
| TMS | 10R | Test mode select. This is the command input for the TAP controller state machine. | |
| TDI | 11R | Test data input. This is the input side of the serial registers placed between TDI and TDO. The register placed between TDI and TDO is determined by the state of the TAP controller state machine and the instruction that is currently loaded in the TAP instruction. | |
| TDO | 1R | Test data output. Output changes in response to the falling edge of TCK. This is the output side of the serial registers placed between TDI and TDO. | |

Notes:

The device does not have TRST (TAP reset). The Test-Logic Reset state is entered while TMS is held high for five rising edges of TCK. The TAP controller state is also reset on SRAM POWER-UP.

TAP DC Operating Characteristics

(Ta = 0 ~ +70°C @ R1Q*A*****BB-**R** series)

(Ta = -40 ~ +85°C @ R1Q*A*****BB-**I** series)

(V_{DD} = 1.8V ±0.1V)

| Parameter | Symbol | Min | Typ | Max | Unit | Notes |
|------------------------|------------------|------|-----|-----------------------|------|--|
| Input high voltage | V _{IH} | +1.3 | — | V _{DD} + 0.3 | V | |
| Input low voltage | V _{IL} | -0.3 | — | +0.5 | V | |
| Input leakage current | I _{LI} | -5.0 | — | +5.0 | μA | 0 V ≤ V _{IN} ≤ V _{DD} |
| Output leakage current | I _{LO} | -5.0 | — | +5.0 | μA | 0 V ≤ V _{IN} ≤ V _{DD} , output disabled |
| Output low voltage | V _{OL1} | — | — | 0.2 | V | I _{OLC} = 100 μA |
| | V _{OL2} | — | — | 0.4 | V | I _{OLT} = 2 mA |
| Output high voltage | V _{OH1} | 1.6 | — | — | V | I _{OHC} = 100 μA |
| | V _{OH2} | 1.4 | — | — | V | I _{OHT} = 2 mA |

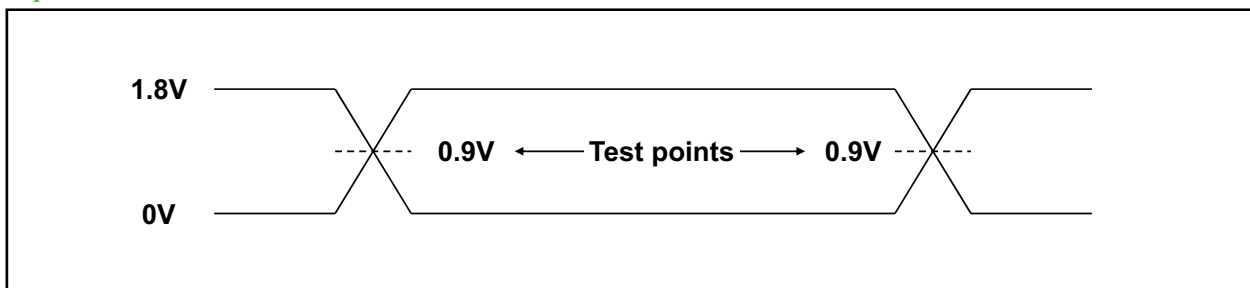
Notes:

- All voltages referenced to V_{SS} (GND).
- At power-up, V_{DD} and V_{DDQ} are assumed to be a linear ramp from 0V to V_{DD}(min.) or V_{DDQ}(min.) within 200ms. During this time V_{DDQ} < V_{DD} and V_{IH} < V_{DDQ}.
During normal operation, V_{DDQ} must not exceed V_{DD}.

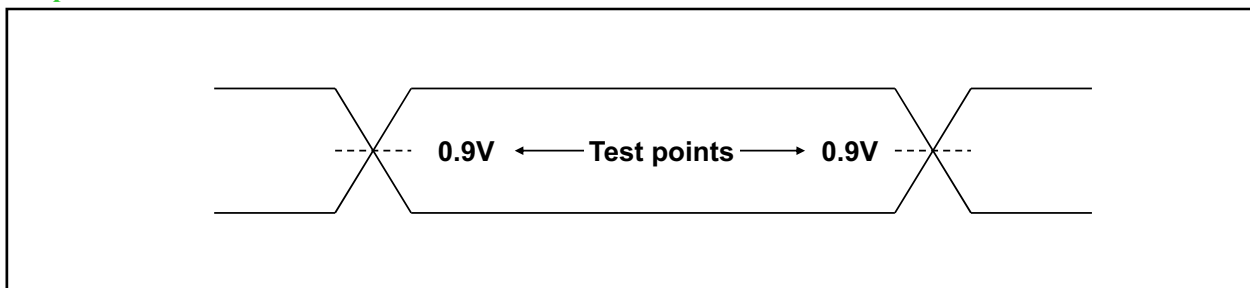
TAPAC Test Conditions

| Parameter | Symbol | Conditions | Unit | Notes |
|---|------------------|-------------|------|-------|
| Input timing measurement reference levels | V_{REF} | 0.9 | V | |
| Input pulse levels | V_{IL}, V_{IH} | 0 to 1.8 | V | |
| Input rise/fall time | t_r, t_f | ≤ 1.0 | ns | |
| Output timing measurement reference levels | | 0.9 | V | |
| Test load termination supply voltage (V_{TT}) | | 0.9 | V | |
| Output load | | See figures | | |

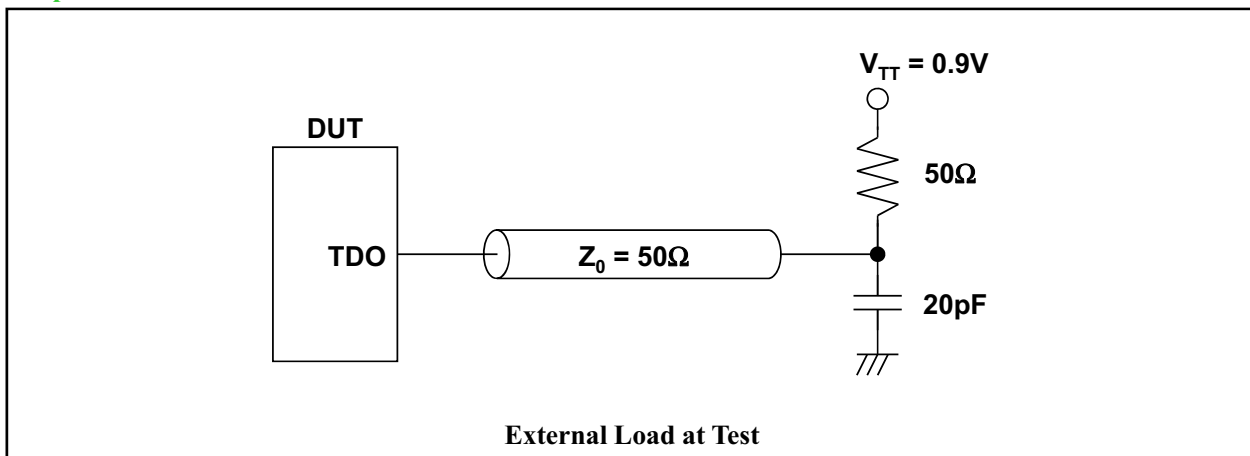
Input waveform



Output waveform



Output load condition



TAPAC Operating Characteristics

(Ta = 0 ~ +70°C @ R1Q*A*****BB-**R** series)

(Ta = -40 ~ +85°C @ R1Q*A*****BB-**I** series)

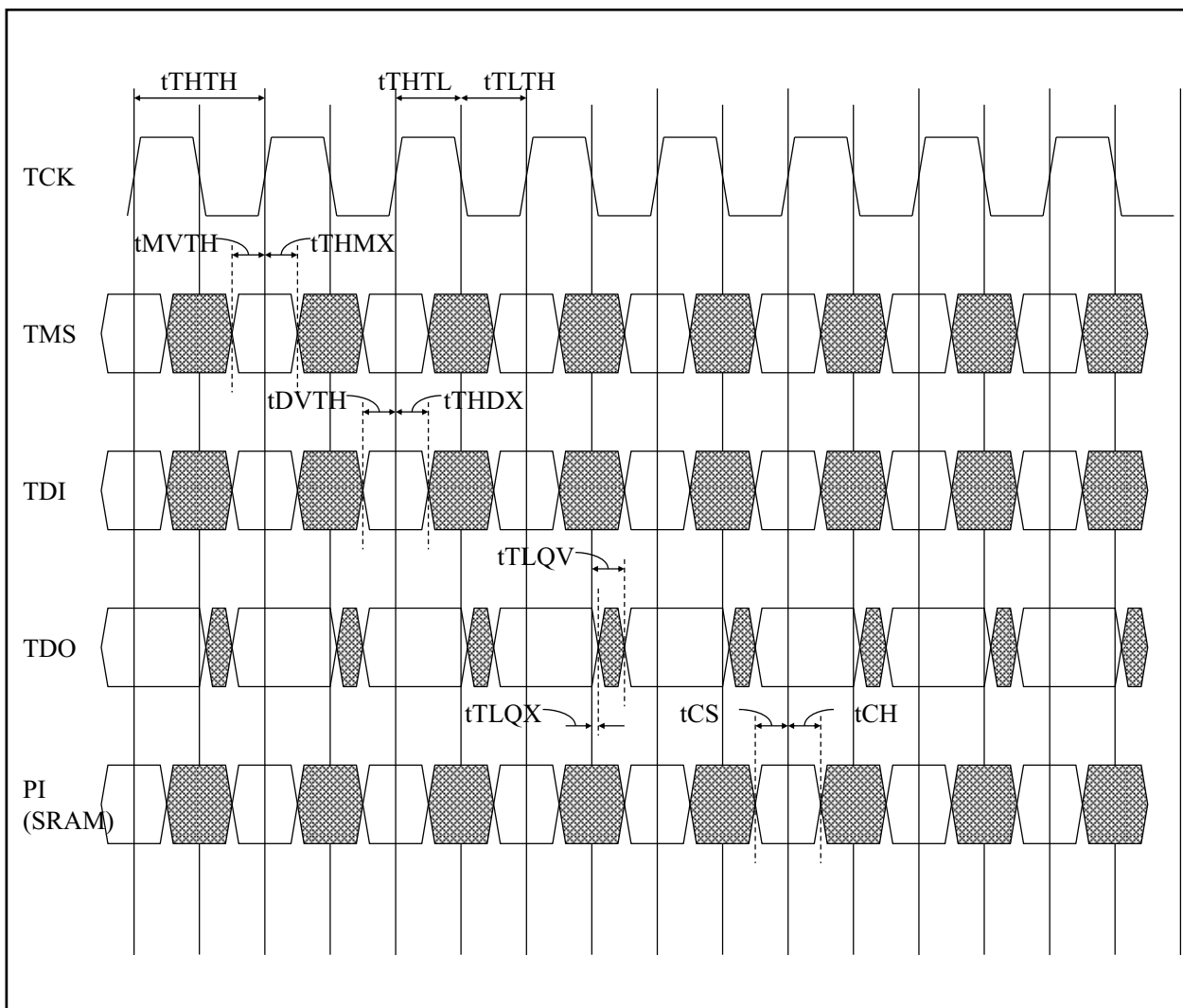
(V_{DD} = 1.8V ±0.1V)

| Parameter | Symbol | Min | Typ | Max | Unit | Notes |
|------------------------------|-------------------|-----|-----|-----|------|-------|
| Test clock (TCK) cycle time | t _{THTH} | 50 | — | — | ns | |
| TCK high pulse width | t _{THTL} | 20 | — | — | ns | |
| TCK low pulse width | t _{TLTH} | 20 | — | — | ns | |
| Test mode select (TMS) setup | t _{MVTH} | 5 | — | — | ns | |
| TMS hold | t _{THMX} | 5 | — | — | ns | |
| Capture setup | t _{CS} | 5 | — | — | ns | 1 |
| Capture hold | t _{CH} | 5 | — | — | ns | 1 |
| TDI valid to TCK high | t _{DVTH} | 5 | — | — | ns | |
| TCK high to TDI invalid | t _{THDX} | 5 | — | — | ns | |
| TCK low to TDO unknown | t _{TLQX} | 0 | — | — | ns | |
| TCK low to TDO valid | t _{TLQV} | — | — | 10 | ns | |

Notes:

- t_{CS} + t_{CH} defines the minimum pause in RAM I/O pad transitions to assure pad data capture.

TAP Controller Timing Diagram



Test Access Port Registers

| Register name | Length | Symbol | Notes |
|------------------------|----------|------------|-------|
| Instruction register | 3 bits | IR [2:0] | |
| Bypass register | 1 bit | BP | |
| ID register | 32 bits | ID [31:0] | |
| Boundary scan register | 109 bits | BS [109:1] | |

TAP Controller Instruction Set

| IR2 | IR1 | IR0 | Instruction | Description | Notes |
|-----|-----|-----|-------------------|--|------------|
| 0 | 0 | 0 | EXTEST | The EXTEST instruction allows circuitry external to the component package to be tested. Boundary scan register cells at output balls are used to apply test vectors, while those at input balls capture test results. Typically, the first test vector to be applied using the EXTEST instruction will be shifted into the boundary scan register using the PRELOAD instruction. Thus, during the Update-IR state of EXTEST, the output driver is turned on and the PRELOAD data is driven onto the output balls. | 1, 2, 3, 5 |
| 0 | 0 | 1 | IDCODE | The IDCODE instruction causes the ID ROM to be loaded into the ID register when the controller is in capture-DR mode and places the ID register between the TDI and TDO balls in shift-DR mode. The IDCODE instruction is the default instruction loaded in at power up and any time the controller is placed in the Test-Logic-Reset state. | |
| 0 | 1 | 0 | SAMPLE-Z | If the SAMPLE-Z instruction is loaded in the instruction register, all RAM outputs are forced to an inactive drive state (high-Z), moving the TAP controller into the capture-DR state loads the data in the RAMs input into the boundary scan register, and the boundary scan register is connected between TDI and TDO when the TAP controller is moved to the shift-DR state. | 3, 4, 5 |
| 0 | 1 | 1 | RESERVED | The RESERVED instructions are not implemented but are reserved for future use. Do not use these instructions. | |
| 1 | 0 | 0 | SAMPLE (/PRELOAD) | When the SAMPLE instruction is loaded in the instruction register, moving the TAP controller into the capture-DR state loads the data in the RAMs input and I/O buffers into the boundary scan register. Because the RAM clock(s) are independent from the TAP clock (TCK) it is possible for the TAP to attempt to capture the I/O ring contents while the input buffers are in transition (i.e., in a metastable state). Although allowing the TAP to SAMPLE metastable input will not harm the device, repeatable results cannot be expected. Moving the controller to shift-DR state then places the boundary scan register between the TDI and TDO balls. | 3, 5 |
| 1 | 0 | 1 | RESERVED | - | |
| 1 | 1 | 0 | RESERVED | - | |
| 1 | 1 | 1 | BYPASS | The BYPASS instruction is loaded in the instruction register when the bypass register is placed between TDI and TDO. This occurs when the TAP controller is moved to the shift-DR state. This allows the board level scan path to be shortened to facilitate testing of other devices in the scan path. | |

Notes:

1. Data in output register is not guaranteed if EXTEST instruction is loaded.
2. After performing EXTEST, power-up conditions are required in order to return part to normal operation.
3. RAM input signals must be stabilized for long enough to meet the TAPs input data capture setup plus hold time (t_{CS} plus t_{CH}). The RAMs clock inputs need not be paused for any other TAP operation except capturing the I/O ring contents into the boundary scan register.
4. Clock recovery initialization cycles are required after boundary scan.
5. For R1QD, R1QE, R1QF, R1QK, R1QL, R1QM, R1QP series, ODT is disabled in EXTEST, SAMPLE-Z or SAMPLE mode.

Boundary Scan Order

| Bit # | Ball ID | Signal names | | | Bit # | Ball ID | Signal names | | |
|-------|---------|--------------------|--------------------|--------------------|-------|---------|--------------|------|------|
| | | x9 | x18 | x36 | | | x9 | x18 | x36 |
| 1 | 6R | /C or NC or ODT | /C or NC or ODT | /C or NC or ODT | 36 | 10E | D3 | D6 | D6 |
| 2 | 6P | C or QVLD | C or QVLD | C or QVLD | 37 | 10D | NC | NC | D15 |
| 3 | 6N | SA | SA | SA | 38 | 9E | NC | NC | Q15 |
| 4 | 7P | SA | SA | SA | 39 | 10C | NC | Q7 | Q7 |
| 5 | 7N | SA | SA | SA | 40 | 11D | NC | D7 | D7 |
| 6 | 7R | SA | SA | SA | 41 | 9C | NC | NC | D16 |
| 7 | 8R | SA | SA | SA | 42 | 9D | NC | NC | Q16 |
| 8 | 8P | SA | SA | SA | 43 | 11B | Q4 | Q8 | Q8 |
| 9 | 9R | SA | SA | SA | 44 | 11C | D4 | D8 | D8 |
| 10 | 11P | Q0 | Q0 | Q0 | 45 | 9B | NC | NC | D17 |
| 11 | 10P | D0 | D0 | D0 | 46 | 10B | NC | NC | Q17 |
| 12 | 10N | NC | NC | D9 | 47 | 11A | CQ | CQ | CQ |
| 13 | 9P | NC | NC | Q9 | 48 | 10A | SA | SA | NC |
| 14 | 10M | NC | Q1 | Q1 | 49 | 9A | SA | SA | SA |
| 15 | 11N | NC | D1 | D1 | 50 | 8B | SA | SA | SA |
| 16 | 9M | NC | NC | D10 | 51 | 7C | SA | SA | SA |
| 17 | 9N | NC | NC | Q10 | 52 | 6C | NC | NC | NC |
| 18 | 11L | Q1 | Q2 | Q2 | 53 | 8A | /R | /R | /R |
| 19 | 11M | D1 | D2 | D2 | 54 | 7A | NC | NC | /BW1 |
| 20 | 9L | NC | NC | D11 | 55 | 7B | /BW | /BW0 | /BW0 |
| 21 | 10L | NC | NC | Q11 | 56 | 6B | K | K | K |
| 22 | 11K | NC | Q3 | Q3 | 57 | 6A | /K | /K | /K |
| 23 | 10K | NC | D3 | D3 | 58 | 5B | NC | NC | /BW3 |
| 24 | 9J | NC | NC | D12 | 59 | 5A | NC | /BW1 | /BW2 |
| 25 | 9K | NC | NC | Q12 | 60 | 4A | /W | /W | /W |
| 26 | 10J | Q2 | Q4 | Q4 | 61 | 5C | SA | SA | SA |
| 27 | 11J | D2 | D4 | D4 | 62 | 4B | SA | SA | SA |
| 28 | 11H | ZQ | ZQ | ZQ | 63 | 3A | SA | SA | SA |
| 29 | 10G | NC | NC | D13 | 64 | 2A | SA | NC | NC |
| 30 | 9G | NC | NC | Q13 | 65 | 1A | /CQ | /CQ | /CQ |
| 31 | 11F | NC | Q5 | Q5 | 66 | 2B | NC | Q9 | Q18 |
| 32 | 11G | NC | D5 | D5 | 67 | 3B | NC | D9 | D18 |
| 33 | 9F | NC | NC | D14 | 68 | 1C | NC | NC | D27 |
| 34 | 10F | NC | NC | Q14 | 69 | 1B | NC | NC | Q27 |
| 35 | 11E | Q3 | Q6 | Q6 | 70 | 3D | NC | Q10 | Q19 |

Boundary Scan Order

| Bit # | Ball ID | Signal names | | | Bit # | Ball ID | Signal names | | |
|-------|---------|--------------|-------|-------|-------|---------|---------------|---------------|---------------|
| | | x9 | x18 | x36 | | | x9 | x18 | x36 |
| 71 | 3C | NC | D10 | D19 | 91 | 2L | Q7 | Q15 | Q24 |
| 72 | 1D | NC | NC | D28 | 92 | 3L | D7 | D15 | D24 |
| 73 | 2C | NC | NC | Q28 | 93 | 1M | NC | NC | D33 |
| 74 | 3E | Q5 | Q11 | Q20 | 94 | 1L | NC | NC | Q33 |
| 75 | 2D | D5 | D11 | D20 | 95 | 3N | NC | Q16 | Q25 |
| 76 | 2E | NC | NC | D29 | 96 | 3M | NC | D16 | D25 |
| 77 | 1E | NC | NC | Q29 | 97 | 1N | NC | NC | D34 |
| 78 | 2F | NC | Q12 | Q21 | 98 | 2M | NC | NC | Q34 |
| 79 | 3F | NC | D12 | D21 | 99 | 3P | Q8 | Q17 | Q26 |
| 80 | 1G | NC | NC | D30 | 100 | 2N | D8 | D17 | D26 |
| 81 | 1F | NC | NC | Q30 | 101 | 2P | NC | NC | D35 |
| 82 | 3G | Q6 | Q13 | Q22 | 102 | 1P | NC | NC | Q35 |
| 83 | 2G | D6 | D13 | D22 | 103 | 3R | SA | SA | SA |
| 84 | 1H | /DOFF | /DOFF | /DOFF | 104 | 4R | SA | SA | SA |
| 85 | 1J | NC | NC | D31 | 105 | 4P | SA | SA | SA |
| 86 | 2J | NC | NC | Q31 | 106 | 5P | SA | SA | SA |
| 87 | 3K | NC | Q14 | Q23 | 107 | 5N | SA | SA | SA |
| 88 | 3J | NC | D14 | D23 | 108 | 5R | SA | SA | SA |
| 89 | 2K | NC | NC | D32 | 109 | — | INTER- NAL | INTER- NAL | INTER- NAL |
| 90 | 1K | NC | NC | Q32 | — | — | — | — | — |

Notes:

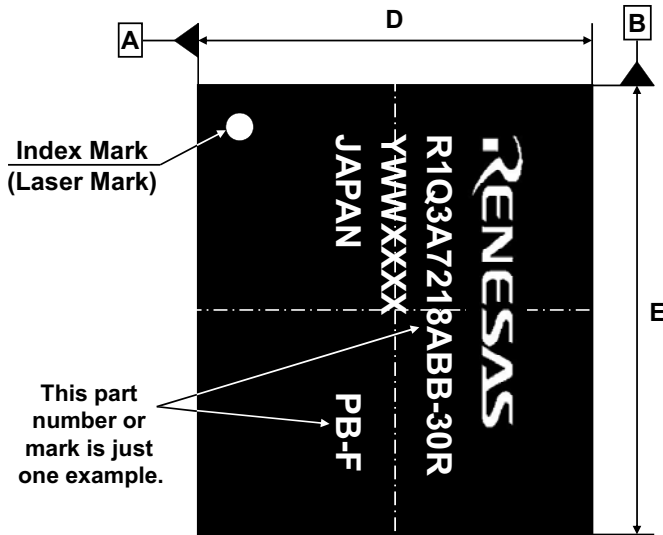
In boundary scan mode,

1. Clock balls (K, /K, C, /C) are referenced to each other and must be at opposite logic levels for reliable operation.
2. CQ and /CQ data are synchronized to the respective C and /C (except EXTEST, SAMPLE-Z).
3. If C and /C tied high, CQ is generated with respect to K and /CQ is generated with respect to /K (except EXTEST, SAMPLE-Z).

Package Dimensions and Marking Information

Both Pb parts and Pb-free parts are available.

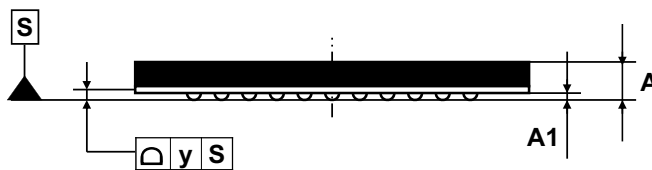
| JEITA Package Code | Renesas Code | Previous Code | Mass (typ.) |
|----------------------|--------------|---------------|-------------|
| P-LBGA165-13x15-1.00 | PLBG0165FE-A | 165FHG | 0.5g |



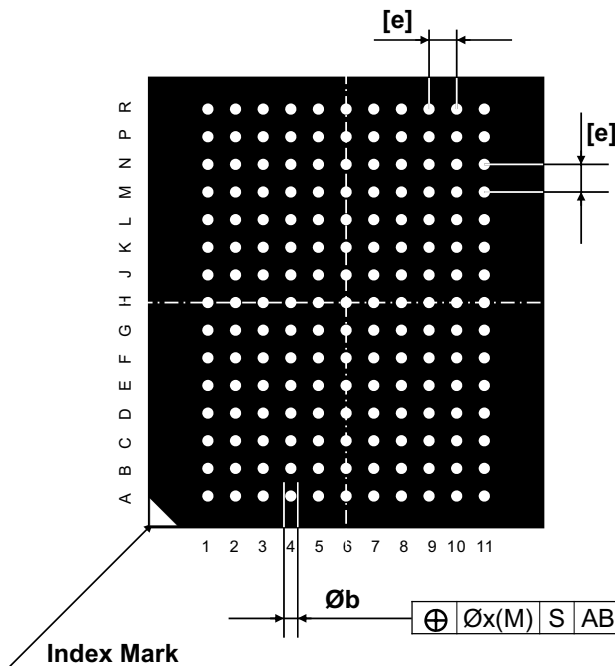
Top View

Marking Information

- 1st row : Vender name (RENESAS)
- 2nd row: Part number
- 3rd row : Y : Year code
WW : Week code
XXXX : Renesas internal use
- 4th row : Country name (JAPAN)
+ "None" --- Pb parts
+ "PB-F" --- Pb-free parts



Side View



Bottom View

| Reference Symbol | Dimension in mm | | |
|------------------|-----------------|------|------|
| | Min | Nom | Max |
| D | 12.9 | 13.0 | 13.1 |
| E | 14.9 | 15.0 | 15.1 |
| A | - | - | 1.4 |
| A1 | 0.31 | 0.36 | 0.41 |
| [e] | - | 1.0 | - |
| b | 0.45 | 0.5 | 0.6 |
| x | - | - | 0.2 |
| y | - | - | 0.15 |

Revision History (1)

| Rev. | Date | # | Comment |
|------------------|-----------|---|--|
| Rev. 0.00a | '08.10.08 | 1 | Initial issue. |
| Rev. 0.00b | '08.10.09 | 1 | Corrected typos in "DC Characteristics": VOH/VOL= VDDQ/2±1.12 → ±0.12. |
| Rev. 0.00c | '08.11.19 | 1 | Added "Speed Bin Table". Added "ODT timing chart" to QDR11+ and DDR11+ series. |
| Rev. 0.00d | '08.11.28 | 1 | Corrected typos in "General Description": ODT pin = Q0~Qn → D0~Dn. |
| | | 2 | Updated "Recommended DC Operating Conditions": Vref =0.68~0.95V → 0.7~0.8V (11+ series). |
| | | 3 | Added comment to "Thermal Resistance" section: These are reference values. |
| Rev. 0.00e | '08.12.07 | 1 | Added "Generation Number Table". |
| Rev. 0.00f -1 | '09.02.09 | 1 | Changed Marking Name in "Part Number Definition Table". |
| | | 2 | Added marking information to "Package Dimension Information" section. |
| | | 3 | Corrected ODT On/Off timing in "ODT pin" table. |
| | | 4 | Updated minimum frequency of QDR11+ and DDR11+ series. |
| | | 5 | Changed pin name in "Pin Arrangement" of DDR11+ series: SA0/SA1 → NC. |
| | | 6 | Added the row to "K Truth Table": RL=2.0 and RL=2.5. |
| Rev. 0.00g -1 | '09.02.24 | 1 | Updated SET-UP cycles: 11+ series DLL lock time = 20us → 2048 cycle. |
| | | 2 | Added comment to "ODT on/off Timing Chart" section: ODT on/off switching timings are edge aligned with CQ or /CQ. |
| | | 3 | Updated "Thermal Resistance". |
| Rev. 0.00h | '09.03.04 | 1 | Added "-50" speed bin to QDR 11 B2 x18/x36 series. |
| Rev. 0.00i | '09.06.15 | 1 | Updated "Package Dimensions": Mass=0.7→0.6g, A(max)=1.46→1.4mm. |
| | | 2 | Updated "Operating/Standby Supply Currents". |
| Rev. 0.01a | '09.10.25 | 1 | Added comment to "Power-up and Initialization Sequence" section: Apply Vref after Vddq or at the same time as Vddq. |
| | | 2 | Updated "Speed Bin Table". |
| Rev. 0.02a | '10.02.01 | 1 | Added "Renesas QDR SRAM Homepage URL" to notes of front page. |
| | | 2 | Updated "Power-up and Initialization Sequence". |
| | | 3 | Updated "DLL Constraints". |
| | | 4 | Updated "Operating Supply Current" and "Standby Supply Current". |
| | | 5 | Updated "Thermal Resistance". |
| | | 6 | Changed remarks of "AC Characteristics" on "Control signals". |
| Rev. 0.03a | '10.04.01 | 1 | Changed company name, RENESAS logo and base color from those of Renesas Technology to Renesas Electronics. |
| | | 2 | Changed vender name marking in "Package Dimensions and Marking Information" section. |
| | | 3 | Added "A" generation to 72M series. |
| Rev. 0.04a | '10.06.10 | 1 | Changed the pin description for NC pin. |
| | | 2 | Changed note 4 of "TAP Controller Instruction Set": "Clock recovery initialization cycles are required after boundary scan" |
| Rev. 0.05a | '10.06.25 | 1 | Changed Vddq range of 11+ series: Vddq=1.5±0.1V → 1.4V ~ Vdd. |
| | | 2 | Added Note.8 and Note.9 to AC Characteristics table for 11+ series. |
| | | 3 | Updated Speed Bin Table for 144M. |
| Rev. 0.05b | '10.07.02 | 1 | Added Note.2 to Generation Number Table. |
| | | 2 | Updated Speed Bin Table for 36M and 72M. |
| Rev. 0.05c | '10.07.24 | 1 | Updated Operating Supply Current and Standby Supply Current Table for 36M and 72M. |
| Rev. 0.06a | '10.09.20 | 1 | Changed Initialization Sequence: Initial cycle of 11+ series = 2048cycles → 20us. |
| Rev. 0.07a | '10.10.06 | 1 | Added Note.9 to AC Characteristics table for 11 series. |
| Rev. 0.07b | '10.10.30 | 1 | Updated AC Characteristics for the series of RL=2.0. |
| | | 2 | Updated Speed Bin Table for 72M/36M/144M. |
| | | 3 | Added R1QNA, R1QPA series to 144M QDR lineup. |
| | | 4 | Changed JTAG/ID Register (ID Code): #27="0": 36M&72M w/o ODT, 144M, 288M "1": 36M&72M w/ ODT #23="0": 144M&288M w/o ODT, 36M, 72M "1": 144M&288M w/ ODT #(26, 25, 24)="100"→"101" (144M), "101"→"110" (288M). |

Revision History (2)

| Rev. | Date | # | Comment |
|-----------|----------|---|---|
| Rev.0.08a | 11.05.23 | 1 | Added Note.7 to tQVLD in AC Characteristics table for II+ series. |
| | | 2 | Changed description of tQVLD in AC Characteristics table for RL=2 series: CQ high to QVLD valid → /CQ high to QVLD valid. |
| | | 3 | Updated Remarks 4 of AC Characteristics table. |
| | | 4 | Updated tKHKH(max) in AC Characteristics table for QDRII+ B2 series. |
| | | 5 | Added 13 x15 mm package lineup to 36M II+ & 72M II/II+ series. |
| Rev.0.08b | 11.07.17 | 1 | Updated "Package Dimensions" for 13 x15 mm package. |
| | | 2 | Updated "Thermal Resistance" for 13 x15 mm package. |
| | | 3 | Changed Title: "Ordering Informaion" → "Part Number Definition", "Speed Bin Table" → "Renesas **M QDR/DDR SRAM Lineup" |
| Rev.0.09a | 11.09.14 | 1 | Updated Specification for ODT Option 2. |
| Rev.0.10a | 11.12.09 | 1 | Updated Part Number Definition table.(Added Note.4) |
| Rev.0.10b | 12.03.12 | 1 | Updated Part Number Definition table.(Added definition to No.10-11) |
| Rev.0.10c | 12.06.05 | 1 | Updated URL for Renesas QDR SRAM Homepage. |
| Rev.0.11 | 13.01.15 | 1 | Updated "Part Number Definition" for 13 x 15 mm Package |

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Tel: +1-408-588-6000, Fax: +1-408-588-6130**Renesas Electronics Canada Limited**1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada
Tel: +1-905-898-5441, Fax: +1-905-898-3220**Renesas Electronics Europe Limited**Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire,
SL8 5FH, U.K
Tel: +44-1628-585-100, Fax: +44-1628-585-900**Renesas Electronics Europe GmbH**Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327**Renesas Electronics (China) Co., Ltd.**7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District,
Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679**Renesas Electronics (Shanghai) Co., Ltd.**Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District,
Shanghai 200120, China
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898**Renesas Electronics Hong Kong Limited**Unit 1601-1613, 16/F., Tower 2, Grand Century Place,
193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2886-9318, Fax: +852 2886-9022/9044**Renesas Electronics Taiwan Co., Ltd.**7F, No. 363 Fu Shing North Road Taipei, Taiwan, R.O.C.
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670**Renesas Electronics Singapore Pte. Ltd.**1 harbourFront Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: +65-6213-0200, Fax: +65-6278-8001**Renesas Electronics Malaysia Sdn.Bhd.**Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18,
Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510**Renesas Electronics Korea Co., Ltd.**11F., Samik Lavied' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku,
Seoul 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141